

RL78/G13A

RENESAS MCU

R01DS0376EJ0110 Rev.1.10 Sep 18, 2020

RL78/G13A microcontrollers share the functionality of RL78/G13 products but have a much (over 40%) lower operating current of 47 μA/MHz (typ.). Operation is guaranteed at ambient temperatures up to 105°C while this is not the case for RL78/G13 products with 384 or 512 Kbytes of code flash memory. RL78/G13A microcontrollers can be used in a wide variety of applications, from home and consumer appliances to industrial equipment.

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- V_{DD} = single power supply voltage of 1.6 to 5.5 V
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.03125 µs: @ 32 MHz operation with high-speed on-chip oscillator) to ultra-low speed (30.5 µs: @ 32.768 kHz operation with subsystem clock)
- · Address space: 1 MB
- General-purpose registers: (8-bit register x 8) x 4 banks
- On-chip RAM: 24 or 32 KB

Code flash memory

- Code flash memory: 384 or 512 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 8 KB
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (typ.)
- Voltage of rewrites: VDD = 1.8 to 5.5 V

High-speed on-chip oscillator

- Select from 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: ±1.0% (V_{DD} = 1.6 to 5.5 V, T_A = -40 to +85°C)

Operating ambient temperature

- T_A = -40 to +85°C (A: Consumer applications)
- T_A = -40 to +105°C (G: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 14 levels)

DMA (Direct Memory Access) controller

- 2/4 channels
- Number of clocks during transfer between 8/16-bit SFR and internal RAM: 2 clocks

Multiplier and divider/multiply-accumulator

- 16 bits x 16 bits = 32 bits (Unsigned or signed)
- 32 bits ÷ 32 bits = 32 bits (Unsigned)
- 16 bits x 16 bits + 32 bits = 32 bits (Unsigned or signed)

Serial interface

- CSI: 4 to 8 channels
- UART/UART (LIN-bus supported): 3 or 4 channels
- I²C/Simplified I²C communication: 5 to 10 channels

Timer

- 16-bit timer: 8 or 12 channels
- 12-bit interval timer: 1 channel
- Real-time clock: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel (operable with the dedicated low-speed on-chip oscillator)

A/D converter

- 8/10-bit resolution A/D converter (VDD = 1.6 to 5.5 V)
- Analog input: 10 to 20 channels
- Internal reference voltage (1.45 V) and temperature sensor Note 1



I/O port

- I/O port: 40 to 92 (N-ch open drain I/O [withstand voltage of 6 V]: 4, N-ch open drain I/O [VDD withstand voltage Note 2/EVDD withstand voltage Note 3]: 10 to 24)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3 V device
- On-chip key interrupt function
- On-chip clock output/buzzer output controller

Others

- On-chip BCD (binary-coded decimal) correction circuit
- **Notes 1.** Can be selected only in HS (high-speed main) mode
 - 2. 44- and 48-pin products
 - 3. 64- and 100-pin products

Remark The functions mounted depend on the product. See **1.6 Outline of Functions**.

O ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G13A				
			44 pins	48 pins	64 pins	100 pins	
512 KB	8 KB	32 KB ^{Note}	R5F140FL	R5F140GL	R5F140LL	R5F140PL	
384 KB	8 KB	24 KB	R5F140FK	R5F140GK	R5F140LK	R5F140PK	

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F140xL (x = F, G, L, P): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/G13A

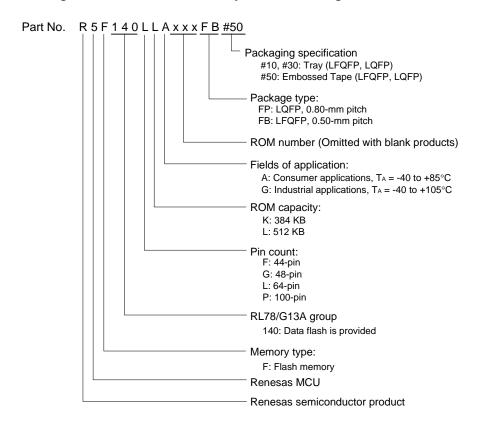


Table 1-1. List of Ordering Part Numbers

Pin count	Package	Data	Fields of	Ordering Part Number
		flash	Application Note	
44 pins	44-pin plastic LQFP	Mounted	Α	R5F140FKAFP#10, R5F140FLAFP#10
	(10 x 10 mm, 0.8-mm pitch)			R5F140FKAFP#30, R5F140FLAFP#30
				R5F140FKAFP#50, R5F140FLAFP#50
			G	R5F140FKGFP#10, R5F140FLGFP#10
				R5F140FKGFP#30, R5F140FLGFP#30
				R5F140FKGFP#50, R5F140FLGFP#50
48 pins	48-pin plastic LFQFP	Mounted	Α	R5F140GKAFB#10, R5F140GLAFB#10
	(7 x 7 mm, 0.5-mm pitch)			R5F140GKAFB#30, R5F140GLAFB#30
				R5F140GKAFB#50, R5F140GLAFB#50
			G	R5F140GKGFB#10, R5F140GLGFB#10
				R5F140GKGFB#30, R5F140GLGFB#30
				R5F140GKGFB#50, R5F140GLGFB#50
64 pins	64-pin plastic LFQFP	Mounted	Α	R5F140LKAFB#10, R5F140LLAFB#10
	(10 x 10 mm, 0.5-mm pitch)			R5F140LKAFB#30, R5F140LLAFB#30
				R5F140LKAFB#50, R5F140LLAFB#50
			G	R5F140LKGFB#10, R5F140LLGFB#10
				R5F140LKGFB#30, R5F140LLGFB#30
				R5F140LKGFB#50, R5F140LLGFB#50
100 pins	100-pin plastic LFQFP	Mounted	А	R5F140PKAFB#10, R5F140PLAFB#10
	(14 x 14 mm, 0.5-mm pitch)			R5F140PKAFB#30, R5F140PLAFB#30
				R5F140PKAFB#50, R5F140PLAFB#50
			G	R5F140PKGFB#10, R5F140PLGFB#10
				R5F140PKGFB#30, R5F140PLGFB#30
				R5F140PKGFB#50, R5F140PLGFB#50

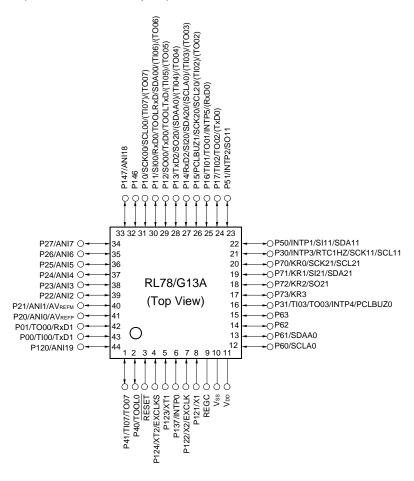
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13A.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

1.3.1 44-pin products

• 44-pin plastic LQFP (10 × 10 mm, 0.8-mm pitch)



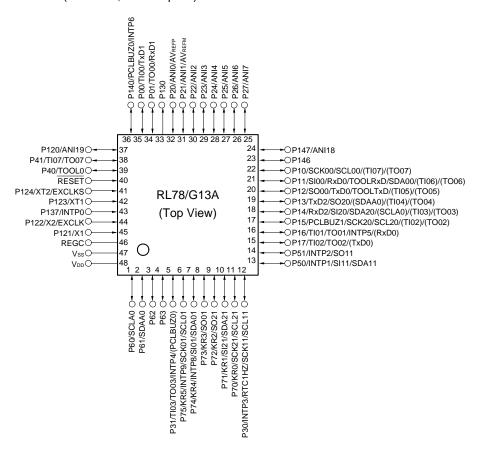
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

 Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13A User's Manual.

1.3.2 48-pin products

• 48-pin plastic LFQFP (7 x 7 mm, 0.5-mm pitch)



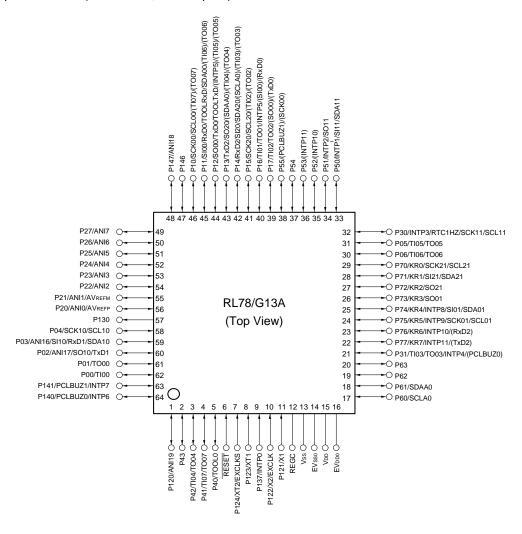
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

 Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13A User's Manual.

1.3.3 64-pin products

• 64-pin plastic LFQFP (10 x 10 mm, 0.5-mm pitch)



Cautions 1. Make EVsso pin the same potential as Vss pin.

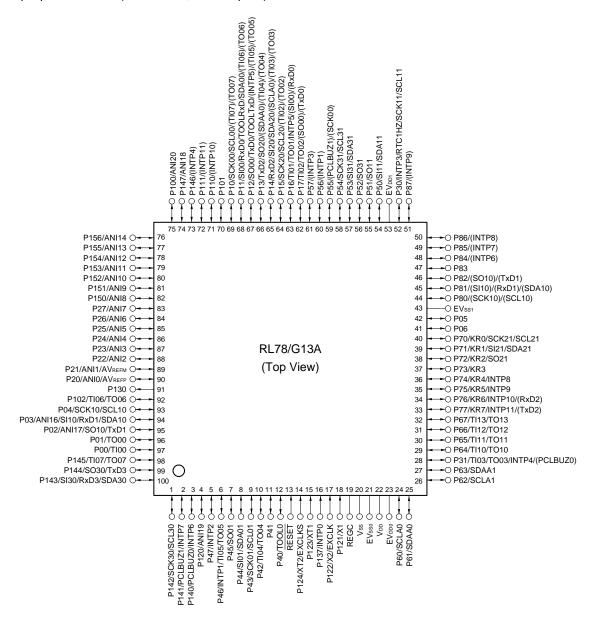
- 2. Make VDD pin the potential that is no less than EVDDO pin.
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the Vss and EV_{SS0} pins to separate ground lines.
- 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13A User's Manual.

1.3.4 100-pin products

• 100-pin plastic LFQFP (14 x 14 mm, 0.5-mm pitch)



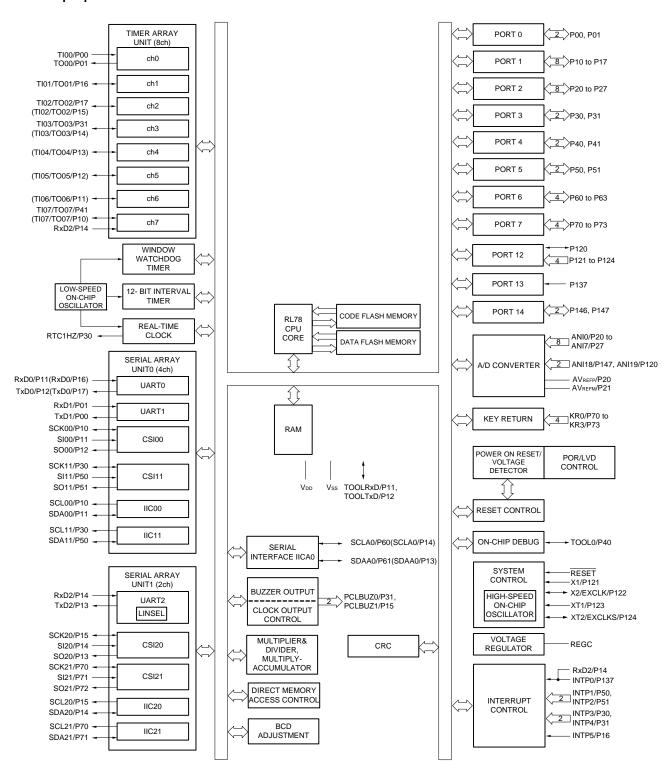
- Cautions 1. Make EVsso and EVsso pins the same potential as Vss pin.
 - 2. Make VDD pin the potential that is no less than EVDD0 and EVDD1 pins (EVDD0 = EVDD1).
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the Vss, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 - 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13A User's Manual.

1.4 Pin Identification

ANI0 to ANI14,		REGC:	Regulator capacitance
ANI16 to ANI20:	Analog input	RESET:	Reset
AVREFM:	A/D converter negative	RTC1HZ:	Real-time clock correction clock
	reference voltage input		(1 Hz) output
AVREFP:	A/D converter positive	RxD0 to RxD3:	Receive data
	reference voltage input	SCLA0, SCLA1,	
EVDD0, EVDD1:	Power supply for port	SCK00, SCK01, SCK10,	
EVsso, EVss1:	Ground for port	SCK11, SCK20, SCK21,	
EXCLK:	External clock input (Main	SCK30, SCK31:	Serial clock input/output
	system clock)	SCL00, SCL01, SCL10,	
EXCLKS:	External clock input	SCL11, SCL20, SCL21,	
	(Subsystem clock)	SCL30, SCL31:	Serial clock output
INTP0 to INTP11:	Interrupt request from	SDAA0, SDAA1, SDA00,	
	peripheral	SDA01, SDA10, SDA11,	
KR0 to KR7:	Key return	SDA20, SDA21, SDA30,	
P00 to P06:	Port 0	SDA31:	Serial data input/output
P10 to P17:	Port 1	SI00, SI01, SI10, SI11,	
P20 to P27:	Port 2	SI20, SI21, SI30, SI31:	Serial data input
P30, P31:	Port 3	SO00, SO01, SO10,	
P40 to P47:	Port 4	SO11, SO20, SO21,	
P50 to P57:	Port 5	SO30, SO31:	Serial data output
P60 to P67:	Port 6	TI00 to TI07,	
P70 to P77:	Port 7	TI10 to TI13:	Timer input
P80 to P87:	Port 8	TO00 to TO07,	
P100 to P102:	Port 10	TO10 to TO13:	Timer output
P110, P111:	Port 11	TOOL0:	Data input/output for tool
P120 to P124:	Port 12	TOOLRxD, TOOLTxD:	Data input/output for external device
P130, P137:	Port 13	TxD0 to TxD3:	Transmit data
P140 to P147:	Port 14	V _{DD} :	Power supply
P150 to P156:	Port 15	Vss:	Ground
PCLBUZ0, PCLBUZ1:	Programmable clock	X1, X2:	Crystal oscillator (main system clock)
	output/buzzer output	XT1, XT2:	Crystal oscillator (subsystem clock)

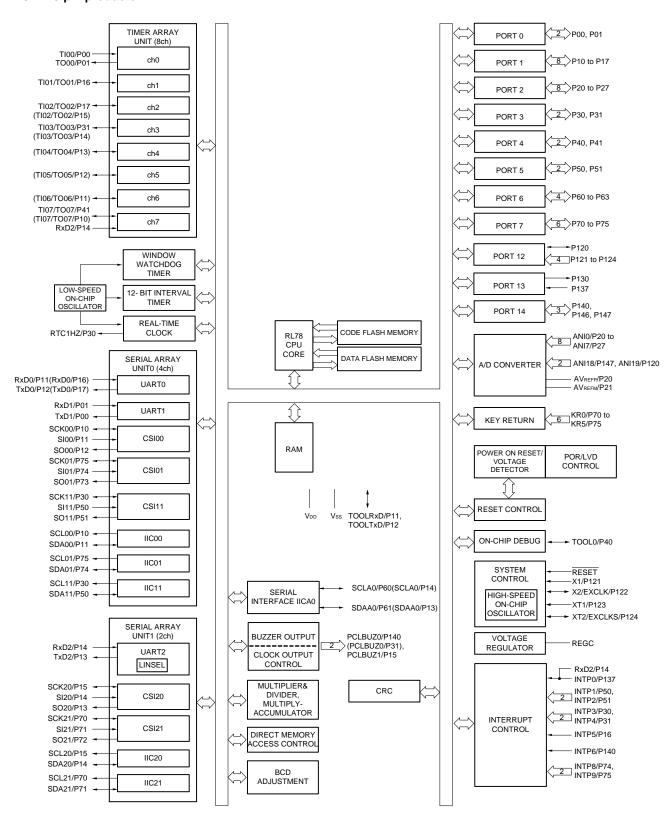
1.5 Block Diagram

1.5.1 44-pin products



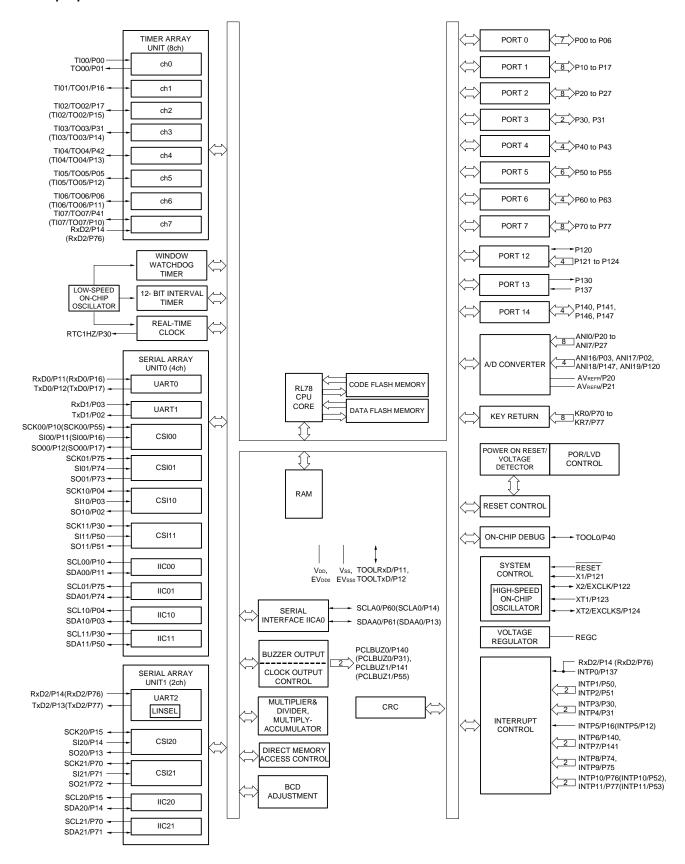
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13A User's Manual.

1.5.2 48-pin products



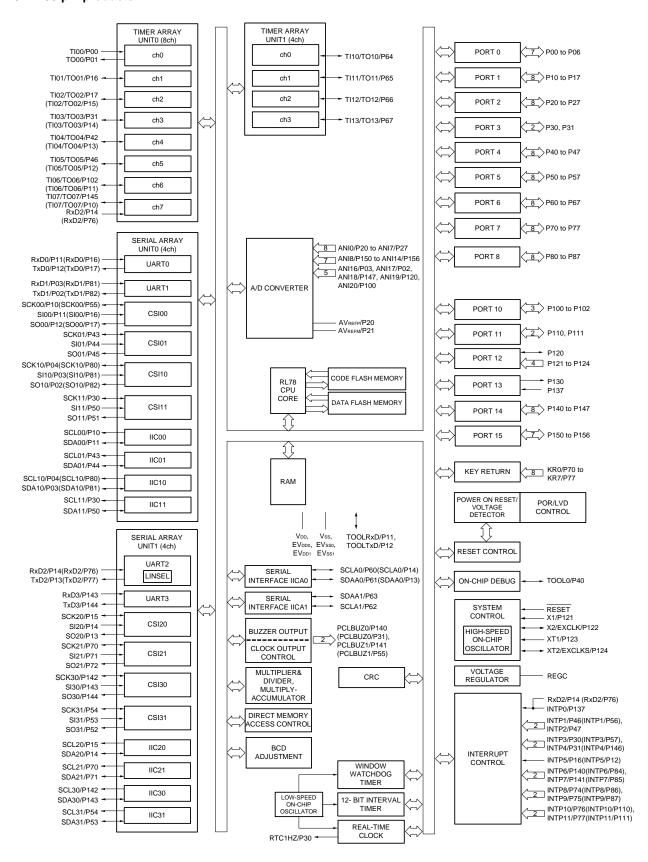
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13A User's Manual.

1.5.3 64-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13A User's Manual.

1.5.4 100-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13A User's Manual.

1. OUTLINE RL78/G13A

1.6 Outline of Functions

[44-pin, 48-pin, 64-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set

(1/2)

				(1/2)			
	Item	44-pin	48-pin	64-pin			
		R5F140Fx	R5F140Gx	R5F140Lx			
Code flash memory (KB)		384, 512	384, 512	384, 512			
Data flash me	mory (KB)	8	8	8			
RAM (KB)		24, 32 ^{Note 1}	24, 32 ^{Note 1}	24, 32 ^{Note 1}			
Address space	e	1 MB					
Main system clock	High-speed system clock High-speed on-chip	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)					
	oscillator	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)					
Subsystem clo	ock	XT1 (crystal) oscillation, extern 32.768 kHz	al subsystem clock input (EXCL	.KS)			
Low-speed on	-chip oscillator	15 kHz (typ.)					
General-purpo	ose registers	(8-bit register × 8) × 4 banks					
Minimum instr	ruction execution time	0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)					
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)					
		30.5 μs (Subsystem clock: fsuB = 32.768 kHz operation)					
Instruction set		 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 					
I/O port	Total	40	44	58			
	CMOS I/O	31 (N-ch O.D. I/O [V _{DD} withstand voltage]: 10)	34 (N-ch O.D. I/O [Vpb withstand voltage]: 11)	48 (N-ch O.D. I/O [Vpp withstand voltage]: 15)			
	CMOS input	5	5	5			
	CMOS output	_	1	1			
	N-ch O.D. I/O (withstand voltage: 6 V)	4	4	4			
Timer	16-bit timer	8 channels					
	Watchdog timer	1 channel					
	Real-time clock (RTC)	1 channel					
	12-bit interval timer (IT)	1 channel					
	Timer output	5 channels (PWM outputs: 4 Note 8 channels (PWM outputs: 7 Note	2), Note 3	8 channels (PWM outputs: 7 Note 2)			
	RTC output	1 channel ◆ 1 Hz (subsystem clock: fsuB = 32.768 kHz)					

Notes 1.

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below. R5F140xL (x = F, G, L): Start address F7F00H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).

The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13A User's Manual).

When setting to PIOR = 1

(2/2)

				(2/2)		
Item		44-pin 48-pin 64-pin				
		R5F140Fx	R5F140Gx	R5F140Lx		
Clock output/buzzer output		2	2	2		
		(Main system clock: fmain =)	2.048 kHz, 4.096 kHz, 8.192 k			
8/10-bit resolution A/D conv	erter	10 channels	10 channels	12 channels		
Serial interface		[44-pin products]				
		CSI: 1 channel/simplified I ²	C: 1 channel/UART: 1 channel C: 1 channel/UART: 1 channel ² C: 2 channels/UART (UART su	pporting LIN-bus): 1 channel		
		 CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [64-pin products] 				
		 CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel 				
	I ² C bus	1 channel	1 channel	1 channel		
Multiplier and divider/multip	ly-accumulator	 16 bits x 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits x 16 bits + 32 bits = 32 bits (Unsigned or signed) 				
DMA controller		2 channels				
Vectored	Internal	27	27	27		
interrupt sources	External	7	10	13		
Key interrupt		4	6	8		
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access				
Power-on-reset circuit		 Power-on-reset: 1.51 V (typ.) Power-down-reset: 1.50 V (typ.) 				
Voltage detector		 Rising edge: 1.67 V to 4.06 V (14 stages) Falling edge: 1.63 V to 3.98 V (14 stages) 				
On-chip debug function		Provided				
Power supply voltage		V _{DD} = 1.6 to 5.5 V (T _A = -40 to +85°C)				
		$V_{DD} = 2.4 \text{ to } 5.5 \text{ V } (T_A = -40 \text{ to } +105^{\circ}\text{C})$				
Operating ambient tempera	ture	T _A = -40 to +85°C (A: Consumer applications) T _A = -40 to +105°C (G: Industrial applications)				

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

[100-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

		(1/2)			
	Item	100-pin			
		R5F140Px			
Code flash me	emory (KB)	384, 512			
Data flash me	emory (KB)	8			
RAM (KB)		24, 32 ^{Note 1}			
Address space	e	1 MB			
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)			
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)			
Subsystem cl	ock	XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz			
Low-speed or	n-chip oscillator	15 kHz (typ.)			
General-purp	ose register	(8-bit register x 8) x 4 banks			
Minimum inst	ruction execution time	0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)			
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)			
		30.5 μs (Subsystem clock: fsuB = 32.768 kHz operation)			
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 			
I/O port	Total	92			
	CMOS I/O	82 (N-ch O.D. I/O [EVDD withstand voltage]: 24)			
	CMOS input	5			
	CMOS output	1			
	N-ch O.D. I/O (withstand voltage: 6 V)	4			
Timer	16-bit timer	12 channels			
	Watchdog timer	1 channel			
	Real-time clock (RTC)	1 channel			
	12-bit interval timer (IT)	1 channel			
	Timer output	12 channels (PWM outputs: 10 Note 2)			
	RTC output	1 channel ■ 1 Hz (subsystem clock: fsuB = 32.768 kHz)			

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F140xL (x = P): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

2. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13A User's Manual).

(2/2)

		(2/2)			
Item		100-pin			
		R5F140Px			
Clock output/buzz	er output	2			
		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: fsub = 32.768 kHz operation) 			
8/10-bit resolution	A/D converter	20 channels			
Serial interface		[100-pin products]			
00.00.		 CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel 			
	I ² C bus	2 channels			
Multiplier and divid	der/multiply-	• 16 bits × 16 bits = 32 bits (Unsigned or signed)			
accumulator		• 32 bits ÷ 32 bits = 32 bits (Unsigned)			
		• 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed)			
DMA controller		4 channels			
Vectored	Internal	37			
interrupt sources	External	13			
Key interrupt		8			
Reset		 Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access 			
Power-on-reset ci	rcuit	 Power-on-reset: 1.51 V (typ.) Power-down-reset: 1.50 V (typ.) 			
Voltage detector		 Rising edge: 1.67 V to 4.06 V (14 stages) Falling edge: 1.63 V to 3.98 V (14 stages) 			
On-chip debug function		Provided			
Power supply volt	age	V _{DD} = 1.6 to 5.5 V (T _A = -40 to +85°C)			
		$V_{DD} = 2.4 \text{ to } 5.5 \text{ V } (T_A = -40 \text{ to } +105^{\circ}\text{C})$			
Operating ambien	t temperature	T _A = -40 to +85°C (A: Consumer applications) T _A = -40 to +105°C (G: Industrial applications)			

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

<R> 2. ELECTRICAL SPECIFICATIONS ($T_A = -40 \text{ to } +85^{\circ}\text{C}$)

This chapter describes the following electrical specifications.

Target products A: Consumer applications $T_A = -40$ to $+85^{\circ}$ C R5F140xxAxx

- G: Industrial applications when $T_A = -40$ to $+105^{\circ}$ C products is used in the range of $T_A = -40$ to $+85^{\circ}$ C R5F140xxGxx
- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EV_{DD0}, EV_{DD1}, EV_{SS0}, or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD}, or replace EV_{SS0} and EV_{SS1} with V_{SS}.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product in the RL78/G13A User's Manual.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EVDD0 = EVDD1	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.1 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VII	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2}	V
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo ₁	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2}	V
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} +0.3 Note 2	V
Analog input voltage	Vai1	ANI16 to ANI20	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V
	V _{Al2}	ANI0 to ANI14	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 $^{\text{Notes 2, 3}}$	V

- Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** AV_{REF} (+) : Positive reference voltage of the A/D converter.
 - 3. Vss: Reference voltage

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	–70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	loL1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	100	mA
	lo _{L2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	Та	In normal operation	on mode	-40 to +85	°C
temperature		In flash memory p	In flash memory programming mode		
Storage temperature	T _{stg}			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/ crystal resonator	2.7 V ≤ V _{DD} ≤ 5.5 V	1.0		20.0	MHz
frequency (fx) ^{Note}		2.4 V ≤ V _{DD} < 2.7 V	1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2.4 V	1.0		8.0	MHz
		1.6 V ≤ V _{DD} < 1.8 V	1.0		4.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator** in the RL78/G13A User's Manual.

2.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін		1		32	MHz
High-speed on-chip oscillator clock frequency accuracy			-1.0		+1.0	%
Low-speed on-chip oscillator clock frequency	fıL			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	1.6 V ≤ EV _{DD0} ≤ 5.5 V			-10.0 Note 2	mA
		Total of P00 to P04, P40 to P47, P102,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			-55.0	mA
		P120, P130, P140 to P145 (When duty ≤ 70% Note 3)	2.7 V ≤ EV _{DD0} < 4.0 V			-10.0	mA
			1.8 V ≤ EV _{DD0} < 2.7 V			-5.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			-80.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111,	2.7 V ≤ EV _{DD0} < 4.0 V			-19.0	mA
		P146, P147	1.8 V ≤ EV _{DD0} < 2.7 V			-10.0	mA
		(When duty ≤ 70% Note 3)	1.6 V ≤ EV _{DD0} < 1.8 V			-5.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ EV _{DD0} ≤ 5.5 V			-135.0 Note 4	mA
	І он2	Per pin for P20 to P27, P150 to P156	1.6 V ≤ V _{DD} ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V _{DD} ≤ 5.5 V			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(loh \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. The applied current for the products for industrial application (R5F140xxGxx) is -100 mA.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	IOL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		P102, P120, P130, P140 to P145 (When duty ≤ 70% Note 3)	4.0 V ≤ EV _{DD0} ≤ 5.5 V			70.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V			15.0	mA
			1.8 V ≤ EV _{DD0} < 2.7 V			9.0	mA
			1.6 V ≤ EV _{DD0} < 1.8 V			4.5	mA
		Total of P05, P06, P10 to P17, P30,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			80.0	mA
		P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101,	2.7 V ≤ EV _{DD0} < 4.0 V			35.0	mA
		P110, P111, P146, P147	1.8 V ≤ EV _{DD0} < 2.7 V			20.0	mA
		(When duty ≤ 70% Note 3)	1.6 V ≤ EV _{DD0} < 1.8 V			10.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				150.0	mA
	lo _{L2}	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	1.6 V ≤ V _{DD} ≤ 5.5 V			5.0	mA

- Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
 - 2. However, do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (3/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8EVDD0		MAX. EVDDO EVDDO EVDDO VDD 6.0 VDD 0.2EVDDO	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2		EV _{DD0}	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	2.0		EV _{DD0}	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	1.5		EV _{DD0}	V
	VIH3	P20 to P27, P150 to P156			V		
	V _{IH4}	P60 to P63	0.7EV _{DD0}		6.0	V	
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLKS	, RESET	0.8V _{DD}		EVDDO EVDDO EVDDO VDD 6.0 VDD 0.2EVDDO 0.32 0.3VDD	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		6.0 V _{DD} 0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	0		0.32	V
	V _{IL3}	P20 to P27, P150 to P156		0		0.3V _{DD}	V
	V _{IL4}	P60 to P63		0		0.3EV _{DD0}	V
	V _{IL5}	P121 to P124, P137, EXCLK, EXCLKS	, RESET	0		EVDDO EVDDO VDD 6.0 VDD 0.2EVDDO 0.8 0.5 0.32 0.3VDD 0.3EVDDO	V

Caution The maximum value of VIH of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDDO, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (4/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -10.0 mA	EV _{DD0} – 1.5			V
		P70 to P77, P80 to P87, P100 to P102, P110, P111, P120,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	EV _{DD0} - 0.7			V
		P130, P140 to P147	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -2.0 mA	EV _{DD0} - 0.6			V
			1.8 V \leq EV _{DD0} \leq 5.5 V, Іон1 = -1.5 mA	EV _{DD0} - 0.5			V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $\text{I}_{\text{OH1}} = -1.0 \text{ mA}$	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	1.6 V ≤ V _{DD} ≤ 5.5 V, I _{OH2} = -100μ A	V _{DD} - 0.5			V
Output voltage, low	V _{OL1}	' ' '	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 20 mA			1.3	V
		P70 to P77, P80 to P87, P100 to P102, P110, P111, P120,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 8.5 mA			0.7	V
		P130, P140 to P147	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 3.0 mA			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 1.5 mA			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 0.6 mA			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ IoL1 = 0.3 mA			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	$1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $1012 = 400 \mu\text{A}$			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL3 = 15.0 mA			2.0	V
			$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iol3 = 5.0 mA			0.4	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iol3 = 3.0 mA			0.4	V
			1.8 V ≤ EV _{DD0} ≤ 5.5 V, lo _{L3} = 2.0 mA			0.4	V
			1.6 V ≤ EV _{DD0} < 5.5 V, lo _{L3} = 1.0 mA			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (5/5)$

Items	Symbol	Conditi	ons		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішн1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVDDO				1	μА
	ILIH2	P20 to P27, P1 <u>37,</u> P150 to P156, RESET	Vı = Vdd				1	μΑ
	ILIH3 P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLK) EXCLKS) VI = VDD In input port or external clock input			1	μА			
				In resonator connection			10	μΑ
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVsso				-1	μА
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss				-1	μΑ
	Ішз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μA
				In resonator connection			-10	μΑ
On-chip pll-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Vi = EVsso,	, In input port	10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/2)$

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply IDD1	I _{DD1}	Operating		fih = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		1.5		mA
current Note 1		mode			operation	V _{DD} = 3.0 V		1.5		mA
	Nomal V _{DD} = 5.0 V	V _{DD} = 5.0 V		3.4	6.8	mA				
					operation	V _{DD} = 3.0 V		3.4	6.8	mA
				fin = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		2.7	5.3	mA
					operation	V _{DD} = 3.0 V		2.7	5.3	mA
				fih = 16 MHz Note 3	Nomal	V _{DD} = 5.0 V		2	3.8	mA
		operation $V_{DD} = 3$.	V _{DD} = 3.0 V		2	3.8	mA			
			LS (low-	f _{IH} = 8 MHz Note 3	Normal	V _{DD} = 3.0 V		1.1	1.9	mA
			speed main) mode Note 5		operation	V _{DD} = 2.0 V		1.1	1.9	mA
			LV (low-	fin = 4 MHz Note 3	Nomal	V _{DD} = 3.0 V		0.7	1.2	mA
			voltage main) mode Note 5		operation	V _{DD} = 2.0 V		0.7	1.2	mA
	HS (high- f _{MX} = 20 MHz ^{Note 2} , Normal Square wave input	Square wave input		2.2	4.4	mA				
			speed main)	V _{DD} = 5.0 V	operation	Resonator connection		2.3	4.5	mA
			mode Note 5	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		2.2	4.4	mA
			$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		2.3	4.5	mA	
		LS (low- speed main mode ^{Note 5}		$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.2	2.4	mA
				$V_{DD} = 5.0 V$	operation	Resonator connection		1.4	2.6	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		1.2	2.4	mA
				V _{DD} = 3.0 V	operation	Resonator connection		1.4	2.6	mA
			LS (low-	$f_{MX} = 8 MHz^{Note 2}$	Nomal	Square wave input		0.9	1.7	mA
			speed main)	V _{DD} = 3.0 V	operation	Resonator connection		1	1.8	mA
			mode	$f_{MX} = 8 MHz^{Note 2}$	Nomal	Square wave input		0.9	1.7	mA
			$V_{DD} = 2.0 \text{ V}$	operation	Resonator connection		1	1.8	mA	
			Subsystem clock	fsub = 32.768 kHz	Normal operation	Square wave input		4	5.5	μΑ
			operation	T _A = -40°C		Resonator connection		4	5.7	μΑ
				f _{SUB} = 32.768 kHz Note 4	Normal operation	Square wave input		4.2	6.7	μΑ
				T _A = +25°C	op or all or	Resonator connection		4.3	6.9	μΑ
				f _{SUB} = 32.768 kHz Note 4	Normal operation	Square wave input		4.5	9.3	μΑ
				T _A = +50°C	0,00001	Resonator connection		4.7	9.5	μΑ
		f _{SUB} = 32.768 kH Note 4 T _A = +70°C	fsuB = 32.768 kHz	Normal operation	Square wave input		5.3	15.8	μΑ	
					0,00001	Resonator connection		5.6	16	μΑ
				fsub = 32.768 kHz	Normal operation	Square wave input		6.6	25.8	μΑ
				T _A = +85°C	0,00001	Resonator connection		7.1	26	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, EVDD1 or Vss, EVss0, EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}@1 \text{ MHz to } 16 \text{ MHz}$

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V}) (2/2)$

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit		
Supply	Supply IDD2	HALT	HS (high-	f _{IH} = 32 MHz Note 4	V _{DD} = 5.0 V		0.41	1.71	mA		
Current Note 1	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.41	1.71	mA		
Hote 1				f _{IH} = 24 MHz Note 4	V _{DD} = 5.0 V		0.34	1.35	mA		
					V _{DD} = 3.0 V		0.34	1.35	mA		
				f _{IH} = 16 MHz Note 4	V _{DD} = 5.0 V		0.33	1.04	mA		
					V _{DD} = 3.0 V		0.33	1.04	mA		
			LS (low-	f _{IH} = 8 MHz Note 4	V _{DD} = 3.0 V		290	650	μΑ		
			speed main) mode Note 7		V _{DD} = 2.0 V		290	650	μΑ		
			LV (low-	f _{IH} = 4 MHz Note 4	V _{DD} = 3.0 V		270	540	μA		
			voltage main) mode Note 7		V _{DD} = 2.0 V		270	540	μA		
			HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.19	1.05	mA		
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.37	1.26	mA		
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	1.05	mA		
				V _{DD} = 3.0 V	Resonator connection		0.37	1.26	mA		
					$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.12	0.62	mA	
				V _{DD} = 5.0 V	Resonator connection		0.22	0.73	mA		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.12	0.62	mA		
				V _{DD} = 3.0 V	Resonator connection		0.22	0.73	mA		
					, ,	$f_{MX} = 8 MHz^{Note 3},$	Square wave input		100	410	μΑ
			main) mode	V _{DD} = 3.0 V	Resonator connection		200	520	μΑ		
					$f_{MX} = 8 MHz^{Note 3},$	Square wave input		100	410	μΑ	
				V _{DD} = 2.0 V	Resonator connection		200	520	μΑ		
					Subsystem	fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.39	1	μΑ
			clock operation	$T_A = -40^{\circ}C$	Resonator connection		0.48	1.3	μΑ		
			operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.55	2.2	μΑ		
				T _A = +25°C	Resonator connection		0.64	2.5	μΑ		
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.98	4.8	μΑ		
				T _A = +50°C	Resonator connection		1.07	5.1	μA		
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.73	11.3	μΑ		
				T _A = +70°C	Resonator connection		1.82	11.6	μΑ		
			fsub = 32.768 kHz ^{Note 5}	Square wave input		2.73	21.3	μΑ			
				T _A = +85°C	Resonator connection		2.82	21.6	μΑ		
	I _{DD3} Note 6	STOP mode ^{Note 8}	T _A = -40°C				0.26	0.7	μΑ		
		mode	T _A = +25°C				0.42	1.9	μΑ		
			T _A = +50°C				0.85	4.5	μA		
			T _A = +70°C			1.60	11	μA			
			$T_A = +85^{\circ}C$				2.60	21	μΑ		

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, EVDD1 or Vss, EVsso, EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}@1 \text{ MHz to } 16 \text{ MHz}$

LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz

LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

- 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

Peripheral Functions (Common to all products)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	FIL Note 1				0.2		μА
RTC operating current	IRTC Notes 1, 2, 3				0.02		μΑ
12-bit interval timer operating current	Notes 1, 2, 4				0.02		μА
Watchdog timer operating current	WDT Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μΑ
A/D converter	ADC Notes 1, 6	When	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
operating current		conversion at maximum speed	Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	I _{ADREF} Note 1				100		μA
Temperature sensor operating current	I _{TMPS} Note 1				100		μА
LVD operating current	_{LVI} Notes 1, 7				0.02		μА
Self- programming operating current	FSP Notes 1, 9				2.5	12.2	mA
BGO operating current	BGO Notes 1, 8				2.5	12.2	mA
SNOOZE	I _{SNOZ} Note 1	ADC operation	The mode is performed Note 10		0.5	0.6	mA
operating current			The A/D conversion operations are performed, Low voltage mode, AVREFP = $V_{DD} = 3.0 \text{ V}$		0.9	1.1	mA
		CSI/UART operati	on		0.5.	0.62	mA

Notes 1. Current flowing to VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or lDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.

- Notes 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
 - 8. Current flowing only during data flash rewrite.
 - 9. Current flowing only during self programming.
 - 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13A User's Manual.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$

2.4 AC Characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Тсч	CY Main system		HS (high-speed 2.7 V≤VDD≤5.5 V			1	μs
		clock (fmain)	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		operation	LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μs
		Subsystem con operation	lock (fsuв)	1.8 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self	HS (high-speed	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
		programming	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		mode	LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μs
External system clock frequency	fex	2.7 V ≤ V _{DD} ≤	5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} <	2.7 V		1.0		16.0	MHz
		1.8 V ≤ V _{DD} <	2.4 V		1.0		8.0	MHz
		1.6 V ≤ V _{DD} <	1.8 V		1.0		4.0	MHz
	fexs				32		35	kHz
External system clock input high-	texh, texl	2.7 V ≤ V _{DD} ≤ 5.5 V			24			ns
level width, low-level width		$2.4 \text{ V} \leq \text{V}_{DD} < 2.7 \text{ V}$			30			ns
		1.8 V ≤ V _{DD} < 2.4 V			60			ns
		1.6 V ≤ V _{DD} <	1.8 V		120			ns
	texhs, texhs				13.7			μs
TI00 to TI07, TI10 to TI13 input high-level width, low-level width	tтін, tті∟				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO13	fто	HS (high-spe	ed 4.0 V ≤	≦ EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V ≤	≤ EV _{DD0} < 4.0 V			8	MHz
			1.8 V ≤	≤ EV _{DD0} < 2.7 V			4	MHz
			1.6 V ≤	€ EV _{DD0} < 1.8 V			2	MHz
		LS (low-spee	d 1.8 V ≤	≤ EV _{DD0} ≤ 5.5 V			4	MHz
		main) mode	1.6 V ≤	≤ EV _{DD0} < 1.8 V			2	MHz
		LV (low-volta main) mode	ge 1.6 V ≤	≦ EV _{DD0} ≤ 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	HS (high-spe	ed 4.0 V ≤	≤ EV _{DD0} ≤ 5.5 V			16	MHz
frequency		main) mode	2.7 V ≤	≤ EV _{DD0} < 4.0 V			8	MHz
			1.8 V ≤	≤ EV _{DD0} < 2.7 V			4	MHz
			1.6 V ≤	1.6 V ≤ EV _{DD0} < 1.8 V			2	MHz
		LS (low-spee	d 1.8 V ≤	≦ EV _{DD0} ≤ 5.5 V			4	MHz
		main) mode	1.6 V ≤	EV _{DD0} < 1.8 V			2	MHz
		LV (low-volta	ge 1.8 V ≤	≦ EV _{DD0} ≤ 5.5 V			4	MHz
		main) mode	1.6 V s	EVDD0 < 1.8 V			2	MHz
Interrupt input high-level width,	tinth,	INTP0	1.6 V s	≤ V _{DD} ≤ 5.5 V	1			μs
low-level width	t intl	INTP1 to INT	P11 1.6 V s	≦ EV _{DD0} ≤ 5.5 V	1			μs
Key interrupt input low-level width	tĸĸ	KR0 to KR7		≤ EV _{DD0} ≤ 5.5 V	250			ns
			1.6 V s	≤ EV _{DD0} < 1.8 V	1			μs
RESET low-level width	trsl				10			μs

(Note and Remark are listed on the next page.)

Note The following conditions are required for low voltage interface when $E_{VDDO} < V_{DD}$

1.8 V \leq EV_{DD0} < 2.7 V : MIN. 125 ns 1.6 V \leq EV_{DD0} < 1.8 V : MIN. 250 ns

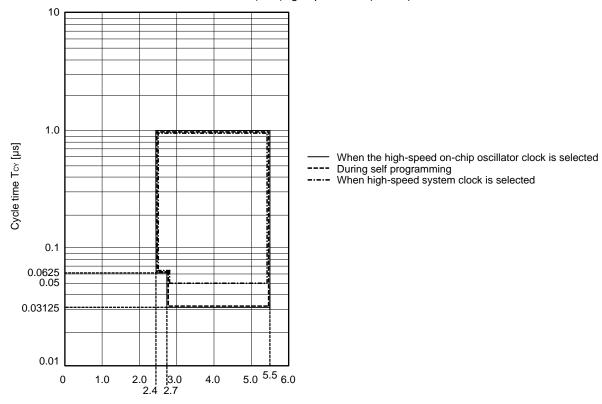
Remark fmck: Timer array unit operation clock frequency

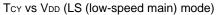
(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

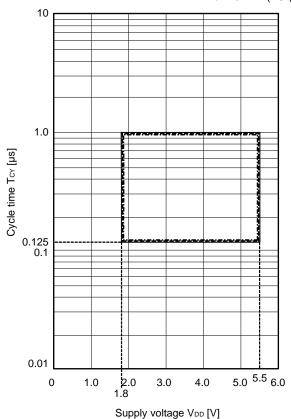
m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

Minimum Instruction Execution Time during Main System Clock Operation



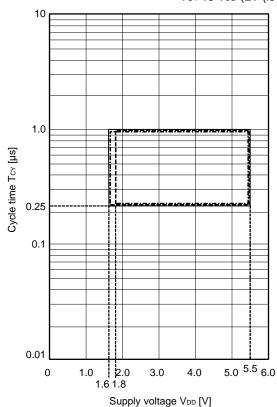






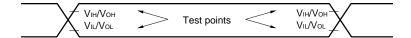
- When the high-speed on-chip oscillator clock is selected
- ---- During self programming
 ---- When high-speed system clock is selected

Tcy vs Vdd (LV (low-voltage main) mode)

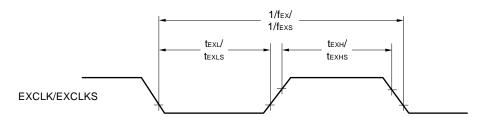


- When the high-speed on-chip oscillator clock is selected
 During self programming
- ---- When high-speed system clock is selected

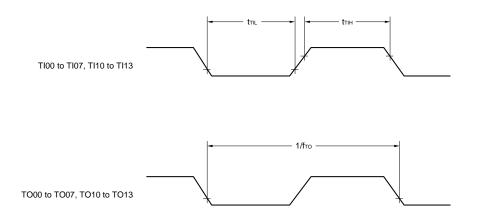
AC Timing Test Points



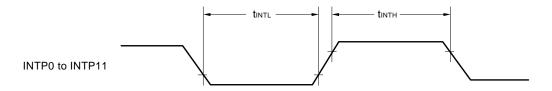
External System Clock Timing



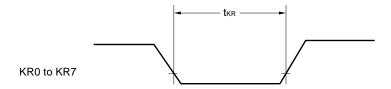
TI/TO Timing



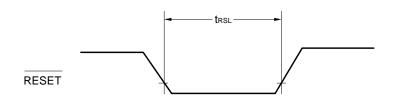
Interrupt Request Input Timing



Key Interrupt Input Timing

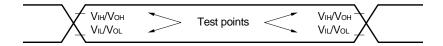


RESET Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		$VDD1 \le VDD \le 5.5 V, Vss$ Conditions		h-speed		v-speed	LV (low	-voltage	Unit
				\ \	Mode		Mode	`	Mode	•
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.4 V≤ EV	_{DD0} ≤ 5.5 V		fMCK/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		5.3		1.3		0.6	Mbps
		1.8 V ≤ EV	_{DD0} ≤ 5.5 V		fMCK/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 3		5.3		1.3		0.6	Mbps
		1.7 V ≤ EV	DD0 ≤ 5.5 V		fMCK/6 Note 2		fMCK/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 3		5.3		1.3		0.6	Mbps
		1.6 V ≤ EV	_{DD0} ≤ 5.5 V		_		fMCK/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 3	-	_		1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when EVDDO < VDD.

 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MAX. } 2.6 \text{ Mbps}$ $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.4 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V} : \text{MAX. } 0.6 \text{ Mbps}$

3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

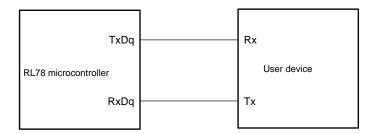
HS (high-speed main) mode: $32 \text{ MHz} (2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V})$

16 MHz $(2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V})$

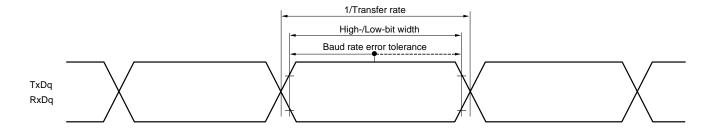
LS (low-speed main) mode: 8 MHz (1.8 V \leq V_{DD} \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq V_{DD} \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high	•		r-speed Mode	`	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fcLk	4.0 V ≤ EV _{DD0} ≤ 5.5 V	62.5		250		500		ns
			2.7 V ≤ EV _{DD0} ≤ 5.5 V	83.3		250		500		ns
SCKp high-/low-level width	tkH1, tkL1	4.0 V ≤ EV _{DD}	o ≤ 5.5 V	tксү1/2 — 7		tксү1/2 — 50		tксү1/2 — 50		ns
		2.7 V ≤ EV _{DD}	₀ ≤ 5.5 V	tксү1/2 — 10		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑)	tsik1	4.0 V ≤ EV _{DD}	o ≤ 5.5 V	23		110		110		ns
Note 1		2.7 V ≤ EV _{DD}	₀ ≤ 5.5 V	33		110		110		ns
SIp hold time (from SCKp↑)	tksi1	2.7 V ≤ EV _{DD}	o ≤ 5.5 V	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF Not	e 4		10		10		10	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. This value is valid only when CSI00's peripheral I/O redirect function is not used.

- 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 1)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	C	Conditions	HS (high main)	•	,	r-speed Mode	LV (low- main)	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fcLk	2.7 V ≤ EV _{DD0} ≤ 5.5 V	125		500		1000		ns
			2.4 V ≤ EV _{DD0} ≤ 5.5 V	250		500		1000		ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	500		500		1000		ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V	1000		1000		1000		ns
			1.6 V ≤ EV _{DD0} ≤ 5.5 V	ı		1000		1000		ns
SCKp high-/low-level width	tkH1,	4.0 V ≤ EV _{DD}	o ≤ 5.5 V	tkcy1/2 –		tксү1/2 — 50		tксу1/2 — 50		ns
		2.7 V ≤ EVDD	o ≤ 5.5 V	tксу1/2 — 18		tксү1/2 — 50		tксу1/2 — 50		ns
		2.4 V ≤ EV _{DD}	o ≤ 5.5 V	tксү1/2 — 38		tксү1/2 — 50		tксү1/2 — 50		ns
		1.8 V ≤ EVDD	o ≤ 5.5 V	tксү1/2 – 50		tксү1/2 — 50		tксү1/2 — 50		ns
		1.7 V ≤ EVDD	o ≤ 5.5 V	tксү1/2 – 100		tксү1/2 — 100		tксу1/2 — 100		ns
		1.6 V ≤ EV _{DD}	o ≤ 5.5 V	I		tксү1/2 — 100		tксу1/2 — 100		ns
SIp setup time	tsıkı	4.0 V ≤ EV _{DD}	o ≤ 5.5 V	44		110		110		ns
(to SCKp↑) Note 1		2.7 V ≤ EVDD	o ≤ 5.5 V	44		110		110		ns
		2.4 V ≤ EVDD	o ≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EVDD	o ≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EVDD	o ≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EVDD	o ≤ 5.5 V	1		220		220		ns
SIp hold time	t KSI1	1.7 V ≤ EV _{DD}	o ≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EVDD	o ≤ 5.5 V	-		19		19		ns
Delay time from SCKp↓ to SOp	tkso1	1.7 V ≤ EV _{DD} C = 30 pF ^{Note}			25		25		25	ns
output Note 3		1.6 V ≤ EV _{DD0} C = 30 pF ^{Note}			_		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Condit	ions	HS (high-s Mo	peed main) ode	,	/-speed Mode	`	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	4.0 V ≤ EV _{DD0} ≤ 5.5 V	20 MHz < fмск	8/fмск		1		-		ns
Note 5			fмск ≤ 20 MHz	6/fмск		6/fмск		6/ƒмск		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	16 MHz < fмск	8/fмск		1		-		ns
			fмcк ≤ 16 MHz	6/fмск		6/fмск		6/fмск		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		6/fмcк and 500		6/fмск and 500		6/fмск and 500		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 \	/	-		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tkH2,	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 7		tксү2/2 -7		tксү2/2 -7		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 8		txcy2/2 -8		tксу2/2 -8		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		tксу2/2 — 18		tксу2/2 - 18		tксү2/2 - 18		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 — 66		tkcy2/2 - 66		tксү2/2 - 66		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 \	1	-		tkcy2/2 - 66		tксү2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

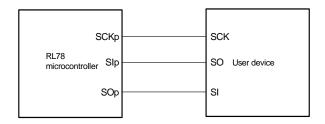
Parameter	Symbol		Conditions	HS (high-sp Mo	,	LS (low-sp Mo	,	LV (low-vol	,	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time	tsik2	2.7 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+20		1/fмск+30		1/fмск+30		ns
(to SCKp \uparrow) Note 1		1.8 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+30		1/fмск+30		1/fмск+30		ns
		1.7 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+40		1/fмск+40		1/fмск+40		ns
		1.6 V ≤ E	EV _{DD0} ≤ 5.5 V	-		1/fмск+40		1/fмск+40		ns
SIp hold time	tksi2	1.8 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+31		1/fмск+31		1/fмск+31		ns
(from SCKp↑) Note 2		1.7 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+ 250		1/fмск+ 250		1/fмск+ 250		ns
		1.6 V ≤ E	EV _{DD0} ≤ 5.5 V	_		1/fмск+ 250		1/fмск+ 250		ns
Delay time from SCKp↓ to SOp	tkso2	C = 30 pF Note 4	2.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+ 44		2/fмск+ 110		2/fмск+ 110	ns
output Note 3			2.4 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+ 75		2/fмск+ 110		2/fмск+ 110	ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+ 110		2/fмск+ 110		2/fмск+ 110	ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+ 220		2/fмск+ 220		2/fмск+ 220	ns
			1.6 V ≤ EV _{DD0} ≤ 5.5 V		-		2/fмск+ 220		2/f _{MCK} + 220	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

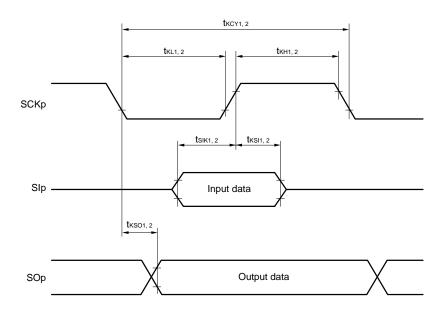
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

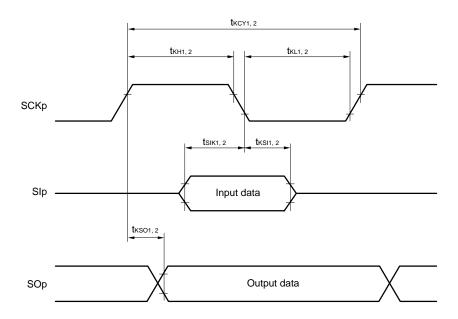
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(5) During communication at same potential (simplified I²C mode) (1/2)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (hig	h-speed Mode	LS (lov	v-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V \leq EV _{DD0} $<$ 2.7 V, C _b = 100 pF, R _b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.7 V \leq EV _{DD0} $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ		250 Note 1		250 Note 1		250 Note 1	kHz
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ		-		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	tLow	2.7 V \leq EV _{DD0} \leq 5.5 V, C _b = 50 pF, R _b = 2.7 kΩ	475		1150		1150		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		1550		1550		ns
		1.7 V ≤ EV _{DD0} < 1.8 V, $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1850		1850		1850		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	-		1850		1850		ns
Hold time when SCLr = "H"	thigh	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	475		1150		1150		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1550		1550		1550		ns
		1.7 V ≤ EV _{DD0} < 1.8 V, $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1850		1850		1850		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	-		1850		1850		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(5) During communication at same potential (simplified I²C mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	\ 0	h-speed Mode	`	v-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1/f _{MCK} + 85 Note2		1/f _{MCK} + 145 Note2		1/f _{MCK} + 145 Note2		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1/f _{MCK} + 145 Note2		1/f _{MCK} + 145 Note2		1/f _{MCK} + 145 Note2		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1/f _{MCK} + 230 Note2		1/fmck + 230 Note2		1/f _{MCK} + 230 Note2		ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1/f _{MCK} + 290 Note2		1/fmck + 290 Note2		1/fmck + 290 Note2		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	-		1/fmck + 290 Note2		1/fmck + 290 Note2		ns
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EV _{DD0} < 2.7 V, $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	0	405	0	405	0	405	ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V ≤ EV _{DD0} < 1.8 V, $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	-	_	0	405	0	405	ns

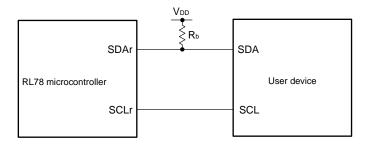
Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

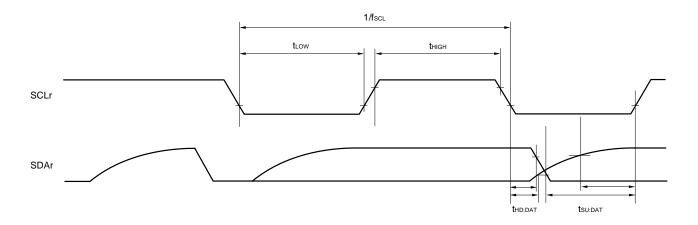
Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (When 44- and 48-pin products)/EVDD tolerance (When 64- and 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

- 2. r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14), h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions			h-speed Mode		/-speed Mode		-voltage Mode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$			fmck/6 Note 1		fMCK/6 Note 1		fmck/6 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps
			1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 4}$		5.3		1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2. Use it with $EV_{DD0} \ge V_b$.
- **3.** The following conditions are required for low voltage interface when EVDDO < VDD.

2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 2.6 Mbps 1.8 V ≤ EV_{DD0} < 2.4 V : MAX. 1.3 Mbps

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: $32 \text{ MHz} (2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V})$

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

LS (low-speed main) mode: $8 \text{ MHz} (1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V})$ LV (low-voltage main) mode: $4 \text{ MHz} (1.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V})$

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 44-and 48-pin products)/EVDD tolerance (When 64- and 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

- 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- 3. fmcκ: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13)
- **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions		speed	high- I main) ode		v-speed Mode	voltage main) Mode		Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$			Note 1		Note 1		Note 1	bps
			2.7 V ≤ V _b ≤ 4.0 V	Theoretical value of the maximum transfer rate		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
				$C_b = 50 \text{ pF}, R_b =$ 1.4 k Ω , $V_b = 2.7 \text{ V}$							
			2.7 V ≤ EV _{DD0} < 4.0 V,			Note 3		Note 3		Note 3	bps
			2.3 V ≤ V _b ≤ 2.7 V	Theoretical value of the maximum transfer rate		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
				$C_b = 50 \text{ pF}, R_b =$ 2.7 k Ω , $V_b = 2.3 \text{ V}$							
			1.8 V ≤ EV _{DD0} < 3.3 V,			Notes		Notes		Notes	bps
			1.6 V ≤ V _b ≤ 2.0 V			5, 6		5, 6		5, 6	
				Theoretical value of the maximum transfer rate		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps
				$C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$							

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1-\frac{2.2}{V_b})\} \times 3} \text{[bps]}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Notes 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DDO} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- 5. Use it with EVDD0 ≥ Vb.
- **6.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V ≤ EV_{DD0} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

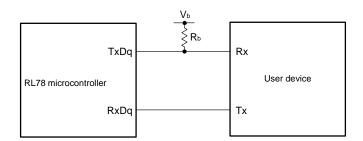
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{1.5}{V_b})\} \times 3} [bps]$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

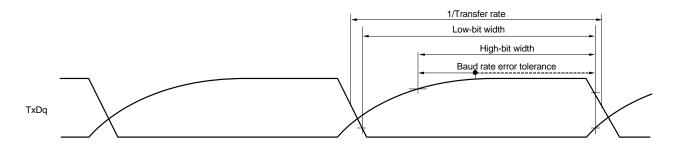
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

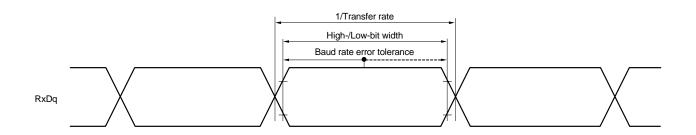
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (Vpd tolerance (When 44-and 48-pin products)/EVpd tolerance (When 64- and 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For Vih and Vill, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remarks 1.** $R_b[\Omega]$:Communication line (TxDq) pull-up resistance,
 - C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high	h-speed Mode	LS (low main)		LV (low- main)	-	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 2/fcLK	$2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	200		1150		1150		ns
			$\begin{split} C_b &= 20 \text{ pF, } R_b = 1.4 \text{ k}\Omega \\ \\ 2.7 \text{ V} &\leq \text{EV}_{\text{DD0}} < 4.0 \text{ V,} \\ \\ 2.3 \text{ V} &\leq \text{V}_b \leq 2.7 \text{ V,} \\ \\ C_b &= 20 \text{ pF, } R_b = 2.7 \text{ k}\Omega \end{split}$	300		1150		1150		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \leq \text{EV}_{\text{DDG}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 2$ $C_{\text{b}} = 20 \text{ pF, R}$	o ≤ 5.5 V, 4.0 V,	tксү1/2 — 50		tксү1/2 — 50		tксү1/2 — 50		ns
		2.7 V \leq EV _{DDO} 2.3 V \leq V _b \leq 2 C _b = 20 pF, R	2.7 V,	tксу1/2 — 120		tксү1/2 — 120		tксү1/2 — 120		ns
SCKp low-level width	t _{KL1}	4.0 V \leq EV _{DDG} 2.7 V \leq V _b \leq 4 C _b = 20 pF, R	o ≤ 5.5 V, 4.0 V,	tксу1/2 — 7		tксү1/2 — 50		tксү1/2 — 50		ns
		$2.7 \text{ V} \le \text{EV}_{DDG}$ $2.3 \text{ V} \le \text{V}_{b} \le 2$ $C_{b} = 20 \text{ pF, R}$	2.7 V,	tксу1/2 — 10		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑) Note 1	tsıkı	$4.0 \text{ V} \leq \text{EV}_{DDG}$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4$ $C_{b} = 20 \text{ pF, R}$	1.0 V,	58		479		479		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2$ $C_{\text{b}} = 20 \text{ pF, R}$	o < 4.0 V, 2.7 V,	121		479		479		ns
SIp hold time (from SCKp†) Note 1	tksi1	$4.0 \text{ V} \leq \text{EV}_{\text{DDG}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 2$ $C_{\text{b}} = 20 \text{ pF, R}$	o ≤ 5.5 V, 4.0 V,	10		10		10		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2$ $C_{\text{b}} = 20 \text{ pF, R}$	o < 4.0 V, 2.7 V,	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$4.0 \text{ V} \leq \text{EV}_{\text{DDG}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 2$ $C_{\text{b}} = 20 \text{ pF, R}$	o ≤ 5.5 V, 4.0 V,		60		60		60	ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2$ $C_{\text{b}} = 20 \text{ pF, R}$	o < 4.0 V, 2.7 V,		130		130		130	ns

(Notes, Caution, and Remarks are listed on the next page.)

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	, ,	h-speed Mode	,	v-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 2	tsıĸ1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	23		110		110		ns
		$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	33		110		110		ns
		$C_b=20~pF,~R_b=2.7~k\Omega$							
SIp hold time (from SCKp↓) Note 2	t KSI1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	10		10		10		ns
		$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	10		10		10		ns
		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$		10		10		10	ns
SOp output Note 2		$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		10		10		10	ns
		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
 - 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 44- and 48-pin products)/EVDD tolerance (When 64- and 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remarks 1. R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),g: PIM and POM number (g = 1)
 - 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00))
 - 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3) (T_A = −40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol		Conditions	, ,	h-speed Mode	LS (low main)	r-speed Mode	,	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	300		1150		1150		ns
			$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	500		1150		1150		ns
			$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note}},$	1150		1150		1150		ns
			$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
SCKp high-level width	tкнı	4.0 V ≤ EV _{DD} 2.7 V ≤ V _b ≤ 4	·	tксү1/2 – 75		tксү1/2 – 75		tксү1/2 — 75		ns
		Сь = 30 pF, F	$R_b = 1.4 \text{ k}\Omega$							
		2.7 V ≤ EV _{DD} 2.3 V ≤ V _b ≤ 3	•	tксү1/2 – 170		tксу1/2 — 170		tксү1/2 – 170		ns
		C _b = 30 pF, F	$R_b = 2.7 \text{ k}\Omega$							
		1.8 V ≤ EV _{DD} 1.6 V ≤ V _b ≤ 3		tксү1/2 — 458		tксү1/2 — 458		tксү1/2 — 458		ns
		C _b = 30 pF, F	$R_b = 5.5 \text{ k}\Omega$							
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD} 2.7 V ≤ V _b ≤ 4	•	tксү1/2 — 12		tксү1/2 — 50		tkcy1/2 - 50		ns
		C _b = 30 pF, F	$R_b = 1.4 \text{ k}\Omega$							
		2.7 V ≤ EV _{DD} 2.3 V ≤ V _b ≤ 3	•	tксү1/2 – 18		tксү1/2 — 50		tксү1/2 – 50		ns
		C _b = 30 pF, F	$R_b = 2.7 \text{ k}\Omega$							
		1.8 V ≤ EV _{DD} 1.6 V ≤ V _b ≤ 2		tксү1/2 — 50		tксү1/2 — 50		tксү1/2 — 50		ns
		C _b = 30 pF, F	$R_b = 5.5 \text{ k}\Omega$							

Note Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 44- and 48-pin products)/EVDD tolerance (When 64- and 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsik1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	81		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	177		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note 2}},$	479		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
SIp hold time (from SCKp↑) Note 1	tksi1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note 2}},$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
Delay time from SCKp↓ to	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$		100		100		100	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
SSP suipat		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		195		195		195	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note 2}},$		483		483		483	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							

Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 44- and 48-pin products)/EVDD tolerance (When 64- and 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions		h-speed Mode	LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 1	tsik1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	44		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	44		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \end{array}$	110		110		110		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
SIp hold time (from SCKp↓) Note 1	t _{KSI1}	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
			19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$		25		25		25	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		25		25		25	ns
		$C_b=30~pF,~R_b=2.7~k\Omega$							
		$\begin{array}{l} 1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \end{array}$		25		25		25	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							

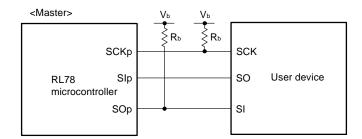
Notes

- 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 2. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 44- and 48-pin products)/EVDD tolerance (When 64- and 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

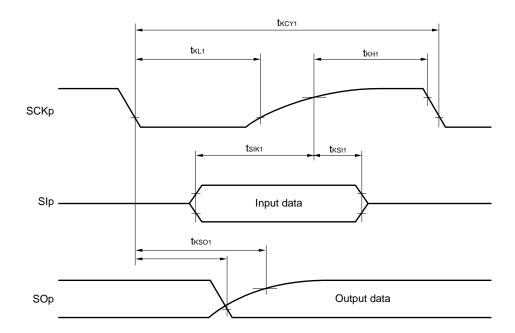
(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

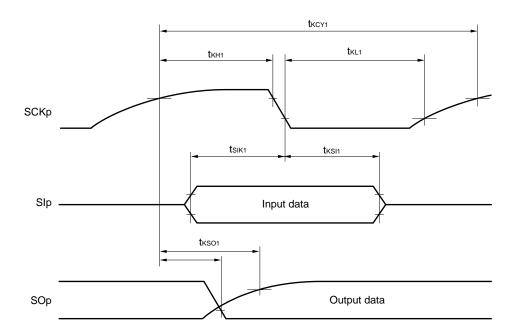


- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 of 48- and 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48- and 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/2)$

Parameter	Symbol	Со	nditions	, ,	h-speed Mode	,	v-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	tkCY2	$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$	24 MHz < fмск	14/ fмск		-		-		ns
			20 MHz < fмcк ≤ 24 MHz	12/ fмск		-		_		ns
			8 MHz < fмcк ≤ 20 MHz	10/ fмск		-		_		ns
			4 MHz < fmck ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			fмск ≤ 4 MHz	6/fмск		10/ fмск		10/ fмск		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	24 MHz < fмск	20/ fмск		-		_		ns
			20 MHz < fмcк ≤ 24 MHz	16/ fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	14/ fмск		-		_		ns
			8 MHz < fmck ≤ 16 MHz	12/ f _{MCK}		-		_		ns
			4 MHz < fmck ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			fмcк ≤ 4 MHz	6/ƒмск		10/ fмск		10/ fмск		ns
		1.8 $V \le EV_{DD0} < 3.3 V$, 1.6 $V \le V_b \le 2.0 V^{\text{Note 2}}$		48/ fмск		-		_		ns
			20 MHz < fмcк ≤ 24 MHz	36/ fмск		-		_		ns
			16 MHz < fмcк ≤ 20 MHz	32/ fмск		_		_		ns
		4	8 MHz < fмcк ≤ 16 MHz	26/ fмск		-		_		ns
			4 MHz < fmck ≤ 8 MHz	16/ fмск		16/ fмск		_		ns
			fmck ≤ 4 MHz	10/ fмск		10/ fмск		10/ fмск		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (2/2) Symbol HS (high-speed LS (low-speed Conditions LV (low-voltage Unit Parameter main) Mode main) Mode main) Mode MIN. MAX. MIN. MIN. MAX. MAX. SCKp high-/low-level $4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ tkcy2/2 tkcy2/2 tkH2. tkcy2/2 ns $2.7 \text{ V} \leq V_b \leq 4.0 \text{ V}$ -50-50width t_{KL2} 12 $2.7 \text{ V} \leq \text{EV}_{DD0} < 4.0 \text{ V},$ tkcy2/2 tkcy2/2 tkcy2/2 ns $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}$ 18 -50-50 $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ tkcy2/2 tkcy2/2 tkcy2/2 ns $1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V}^{\text{Note 2}}$ 50 -50-50Slp setup time tsik2 $4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ 1/fmck 1/fmck 1/fmck ns (to SCKp↑) Note 3 + 30 +20+30 $2.7~V \le V_b \le 4.0~V$ $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ 1/fmck 1/fmck 1/fmck ns + 30 +20+30 $2.3 \text{ V} \leq V_b \leq 2.7 \text{ V}$ $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ 1/fmck 1/fmck 1/fmck $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}^{\text{Note 2}}$ + 30 + 30 +30 SIp hold time $1/f_{MCK} +$ 1/fmck 1/fmck tks12 ns (from SCKp↑) Note 4 + 31 31 +31Delay time from **t**KSO2 $4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ 2/fmck 2/fmck 2/fmck ns SCKp↓ to SOp output $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$ + 120 + 573 +573 Note 5 $2.7 \text{ V} \le \text{EV}_{DD0} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}.$ 2/fmck + 2/fmck 2/fmck + ns $C_b=30~pF,~R_b=2.7~k\Omega$ + 214 573 573 $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ **2/f**мск 2/fmck + 2/fmck + ns $1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}^{\text{Note 2}}$ +573 573 573

Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

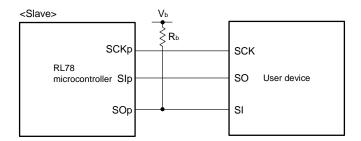
 $C_b=30~pF,~R_b=5.5~k\Omega$

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (Vpd tolerance (for the 44- and 48-pin products)/EVpd tolerance (for the 64- and 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For Vih and Vil, see the DC characteristics with TTL input buffer selected.

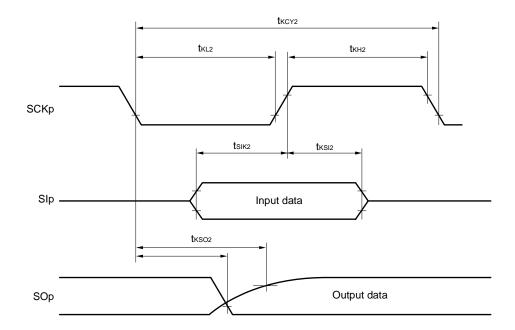
(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

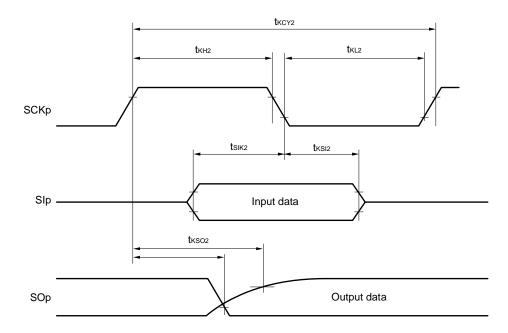


- Remarks 1. $R_b[\Omega]$:Communication line (SOp) pull-up resistance, $C_b[F]$: Communication line (SOp) load capacitance, $V_b[V]$: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48- and 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48- and 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (hig	h-speed Mode	LS (low	v-speed Mode	,	r-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{aligned} 4.0 & \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} & = 50 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega \end{aligned}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:controller} \begin{split} 2.7 & \ V \le EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 50 & \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $		400 Note 1		300 Note 1		300 Note 1	kHz
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $		400 Note 1		300 Note 1		300 ote 1	kHz
		$\begin{split} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega \end{split}$		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$ \begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b = 50 & \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	475		1550		1550		ns
		$ 2.7 \ V \le EV_{DD0} < 4.0 \ V, $ $ 2.3 \ V \le V_b \le 2.7 \ V, $ $ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega $	475		1550		1550		ns
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	1150		1550		1550		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	1150		1550		1550		ns
		$\begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned}$	1550		1550		1550		ns
Hold time when SCLr = "H"	tнідн	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	245		610		610		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	200		610		610		ns
		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ k}\Omega$	675		610		610		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	600		610		610		ns
		$\begin{split} &1.8 \; \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \; \text{V}, \\ &1.6 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \; \text{V}^{\; \text{Note 2}}, \\ &C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 5.5 \; \text{k}\Omega \end{split}$	610		610		610		ns

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

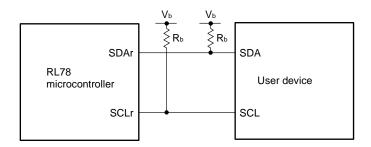
Parameter	Symbol	Conditions	HS (high	•	`	/-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$ \begin{aligned} 4.0 \ V &\leq E V_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1/fмск + 135 Note 3		1/fмск + 190 Note 3		1/fmck + 190 Note 3		kHz
			1/f _{MCK} + 135 Note 3		1/fmck + 190 Note 3		1/fмск + 190 Note 3		kHz
		$ \begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 3		1/fmck + 190 Note 3		1/fмск + 190 Note 3		kHz
			1/f _{MCK} + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
		$ \begin{aligned} &1.8 \; V \leq EV_{DD0} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V^{\text{Note 2}}, \\ &C_b = 100 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned} $	1/f _{MCK} + 190 Note 3		1/fmck + 190 Note 3		1/fмск + 190 Note 3		kHz
Data hold time (transmission)	thd:dat	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	ns
			0	305	0	305	0	305	ns
		$ 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega $	0	355	0	355	0	355	ns
			0	355	0	355	0	355	ns
		$\begin{split} 1.8 \ V & \le EV_{DD0} < 3.3 \ V, \\ 1.6 \ V & \le V_b \le 2.0 \ V^{\text{Note 2}}, \\ C_b & = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	0	405	0	405	0	405	ns

- Notes 1. The value must also be equal to or less than fmck/4.
 - 2. Use it with EV_{DD0} ≥ V_b.
 - 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

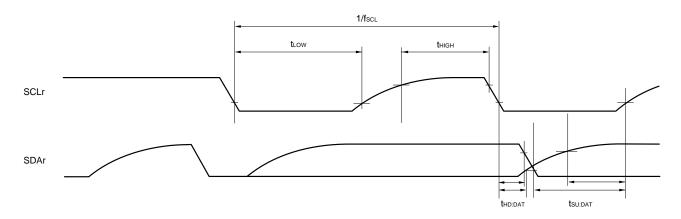
Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 44- and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 44- and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

- 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
- 3. fмск: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13)

2.5.2 Serial interface IICA

(1) I²C standard mode

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	, ,	h-speed Mode	,	v-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode:	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
		fc∟k≥ 1 MHz	1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EV _{DD0} ≤ 5.5 V		_	0	100	0	100	kHz
Setup time of restart	tsu:sta	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
condition		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EV _{DD0} ≤ 5.5	5 V		_	4.7		4.7		μs
Hold time ^{Note 1}	thd:STA	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EV _{DD0} ≤ 5.5	5 V	-	_	4.0		4.0		μs
Hold time when SCLA0 =	tLOW	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
" <u>L</u> "		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EV _{DD0} ≤ 5.9	5 V		_	4.7		4.7		μs
Hold time when SCLA0 =	thigh	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
"H"		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EV _{DD0} ≤ 5.5	5 V		_	4.0		4.0		μs
Data setup time	tsu:dat	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	250		250		250		ns
(reception)		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	250		250		250		ns
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	250		250		250		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5	5 V		_	250		250		ns
Data hold time	thd:dat	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0	3.45	0	3.45	0	3.45	μs
(transmission)Note 2		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0	3.45	0	3.45	0	3.45	μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	0	3.45	0	3.45	0	3.45	μs
		1.6 V ≤ EV _{DD0} ≤ 5.5	5 V		_	0	3.45	0	3.45	μs
Setup time of stop	tsu:sto	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
condition		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EV _{DD0} ≤ 5.5	5 V			4.0		4.0		μs
Bus-free time	t BUF	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EV _{DD0} ≤ 5.5	5 V		_	4.7		4.7		μs

(Notes, Caution and Remark are listed on the next page.)

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - The maximum value (MAX.) of tho:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$

(2) I2C fast mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
		fclk≥ 3.5 MHz	1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart	tsu:sta	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
condition		1.8 V ≤ EV _{DD0} ≤ 5.	1.8 V ≤ EV _{DD0} ≤ 5.5 V			0.6		0.6		μs
Hold time ^{Note 1}	thd:STA	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
Hold time when SCLA0 =	tLOW	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	1.3		1.3		1.3		μs
"L"		1.8 V ≤ EV _{DD0} ≤ 5.	1.8 V ≤ EV _{DD0} ≤ 5.5 V			1.3		1.3		μs
Hold time when SCLA0 =	tніgн	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
"H"		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
Data setup time	tsu:dat	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	100		100		100		μs
(reception)		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	100		100		100		μs
Data hold time	thd:dat	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0	0.9	0	0.9	0	0.9	μs
(transmission)Note 2		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0	0.9	0	0.9	0	0.9	μs
Setup time of stop	tsu:sto	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
condition		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
Bus-free time	t BUF	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	1.3		1.3		1.3		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - The maximum value (MAX.) of tho:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VoH1, VoL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \ pF, \ R_b = 1.1 \ k\Omega$

(3) I²C fast mode plus

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Cond	Conditions		h-speed Mode		r-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode plus: 2 fcLk ≥ 10 MHz	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	1000			-	-	kHz
Setup time of restart condition	t _{SU:STA}	2.7 V ≤ EV _{DD0} ≤ 5.5 '	2.7 V ≤ EV _{DD0} ≤ 5.5 V			_		-		μs
Hold time ^{Note 1}	thd:STA	2.7 V ≤ EV _{DD0} ≤ 5.5 '	V	0.26		_		_	-	μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EV _{DD0} ≤ 5.5 '	V	0.5		-	-	-	-	μs
Hold time when SCLA0 = "H"	tніgн	2.7 V ≤ EV _{DD0} ≤ 5.5 '	V	0.26		_	-	-	-	μs
Data setup time (reception)	tsu:dat	2.7 V ≤ EV _{DD0} ≤ 5.5 '	V	50		=		-	-	μs
Data hold time (transmission) ^{Note 2}	thd:dat	2.7 V ≤ EV _{DD0} ≤ 5.5 '	V	0	0.45	-	-	-	-	μs
Setup time of stop condition	tsu:sto	2.7 V ≤ EV _{DD0} ≤ 5.5 '	V	0.26		-	-	-	-	μs
Bus-free time	tbuf	2.7 V ≤ EV _{DD0} ≤ 5.5 '	V	0.5		-	-	-	-	μs

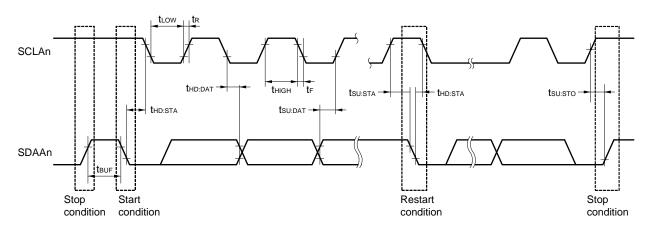
- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VoH1, VoL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: $C_b = 120 \text{ pF}$, $R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



Remark n = 0, 1

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = VBGR
Input channel	Reference voltage (–) = AVREFM	Reference voltage (–) = Vss	Reference voltage (–) = AVREFM
ANI0 to ANI14	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4) .
ANI16 to ANI20	Refer to 2.6.1 (2).		
Internal reference voltage	Refer to 2.6.1 (1).		_
Temperature sensor output			
voltage			

(1) When reference voltage (+)= AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±3.5	LSB
		AVREFP = VDD Note 3	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target pin: ANI2 to ANI14	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs
		10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.375		39	μs
		Target pin: Internal	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μs
	tempe voltag (HS (reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	µs
Zero-scale errorNotes 1, 2	Ezs	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR
		AVREFP = VDD Note 3	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4			±0.50	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR
		AVREFP = VDD Note 3	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4			±0.50	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±2.5	LSB
		AVREFP = VDD Note 3	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±1.5	LSB
		AVREFP = VDD Note 3	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4			±2.0	LSB
Analog input voltage	VAIN	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)			V _{BGR} Note 5		V
		Temperature sensor output (2.4 V ≤ VDD ≤ 5.5 V, HS (h	\	/ _{TMPS25} Note	5	V	

(Notes are listed on the next page.)

- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.
 - Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 - Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.
 - Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 - 4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).
 - 5. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI16 to ANI20

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, 1.6 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditi	ons	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±5.0	LSB
		$EVDD0 = AV_{REFP} = V_{DD}^{Notes 3, 4}$	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
		Target ANI pin : ANI16 to	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
		ANI20	1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
		EVDD0 = AVREFP = VDD Notes 3, 4	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5			±0.60	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
		EVDD0 = AVREFP = VDD Notes 3, 4	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5			±0.60	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±3.5	LSB
		$EVDD0 = AV_{REFP} = V_{DD}^{Notes 3, 4}$	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5			±6.0	LSB
Differential linearity	DLE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±2.0	LSB
error Note 1		$EV_{DD0} = AV_{REFP} = V_{DD}^{Notes 3, 4}$	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5			±2.5	LSB
Analog input voltage	Vain	ANI16 to ANI20		0		AVREFP and EVDD0	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when AVREFP = VDD.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

4. When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.

Overall error: Add ±4.0 LSB to the MAX. value when AVREFP = VDD.

Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AVREFP = VDD.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \leq \text{EV}_{DD0} = \text{EV}_{DD1} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{DD}, \text{Reference voltage (-)} = \text{V}_{SS})$

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall errorNote 1	AINL	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
			$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$ Note 3		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
		Target pin: ANIO to ANI14,	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
		ANI16 to ANI20	1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs
Conversion time	tconv	10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
		Target pin: Internal	2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	1.8 V ≤ VDD ≤ 5.5 V			±0.60	%FSR
			$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$ Note 3			±0.85	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$ Note 3			±0.85	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±6.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ VDD ≤ 5.5 V			±2.0	LSB
			$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$ Note 3			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI14		0		V _{DD}	V
	ANI16 to ANI20			0		EV _{DD0}	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (hig		V _{BGR} Note 4		V	
		Temperature sensor output v (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (hig	V _{TMPS25} Note 4			V	

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).
- 4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI20

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{BGR}^{Note 3}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V}^{Note 4}, \text{HS (high-speed main) mode)}$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	Vain			0		V _{BGR} Note 3	V

- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.
 - 4. When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.
 Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

2.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

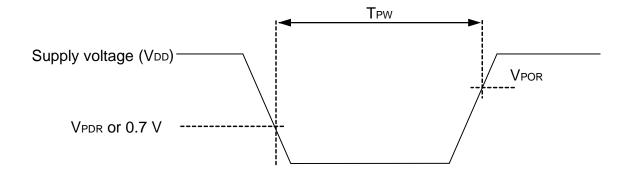
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, TA = +25°C		1.14		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	Fvтмps	Temperature dependence of the temperature sensor		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

2.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	The power supply voltage is rising.	1.47	1.51	1.55	V
	V _{PDR}	The power supply voltage is falling.	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VLVD0	The power supply voltage is rising.	3.98	4.06	4.14	V
		The power supply voltage is falling.	3.90	3.98	4.06	V
	V _{LVD1}	The power supply voltage is rising.	3.68	3.75	3.82	V
		The power supply voltage is falling.	3.60	3.67	3.74	V
	V _{LVD2}	The power supply voltage is rising.	3.07	3.13	3.19	V
		The power supply voltage is falling.	3.00	3.06	3.12	V
	V _{LVD3}	The power supply voltage is rising.	2.96	3.02	3.08	V
		The power supply voltage is falling.	2.90	2.96	3.02	V
	V _{LVD4}	The power supply voltage is rising.	2.86	2.92	2.97	V
		The power supply voltage is falling.	2.80	2.86	2.91	V
	V _{LVD5}	The power supply voltage is rising.	2.76	2.81	2.87	V
		The power supply voltage is falling.	2.70	2.75	2.81	V
	V _{LVD6}	The power supply voltage is rising.	2.66	2.71	2.76	V
		The power supply voltage is falling.	2.60	2.65	2.70	V
	V _{LVD7}	The power supply voltage is rising.	2.56	2.61	2.66	V
		The power supply voltage is falling.	2.50	2.55	2.60	V
	V _{LVD8}	The power supply voltage is rising.	2.45	2.50	2.55	V
		The power supply voltage is falling.	2.40	2.45	2.50	V
	V _{LVD9}	The power supply voltage is rising.	2.05	2.09	2.13	V
		The power supply voltage is falling.	2.00	2.04	2.08	V
	V _L VD10	The power supply voltage is rising.	1.94	1.98	2.02	V
		The power supply voltage is falling.	1.90	1.94	1.98	V
	V _L VD11	The power supply voltage is rising.	1.84	1.88	1.91	V
		The power supply voltage is falling.	1.80	1.84	1.87	V
	V _{LVD12}	The power supply voltage is rising.	1.74	1.77	1.81	V
		The power supply voltage is falling.	1.70	1.73	1.77	V
	V _{LVD13}	The power supply voltage is rising.	1.64	1.67	1.70	V
		The power supply voltage is falling.	1.60	1.63	1.66	V
Minimum pulse width	tıw		300			μs
Detection delay time					300	μs

LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	ditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VLVDA0	VPOC2,	VPOC1, VPOC0 = 0, 0, 0,	falling reset voltage	1.60	1.63	1.66	V
	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	V _L VDA3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V _L VDB0	VPOC2,	VPOC1, VPOC0 = 0, 0, 1,	falling reset voltage	1.80	1.84	1.87	V
	V _{LVDB1}		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
			Falling interrupt voltage	1.90	1.94	1.98	V	
	VLVDB2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	V _{LVDB3}		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	V _{LVDC0}	VPOC2,	VPOC1, VPOC0 = 0, 1, 0,	falling reset voltage	2.40	2.45	2.50	V
	VLVDC1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	V _L VDC3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	V _L VDD0	VPOC2,	VPOC1, VPOC0 = 0, 1, 1,	falling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
VL				Falling interrupt voltage	2.80	2.86	2.91	V
	V _{LVDD2}	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	V _L VDD3	V _{LVDD3}	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

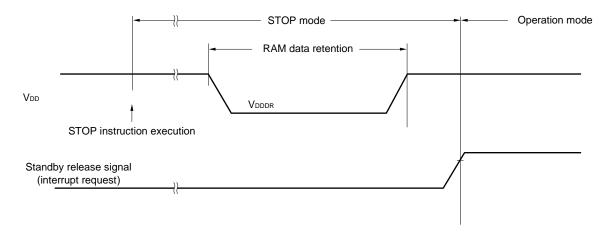
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	1.8 V ≤ VDD ≤ 5.5 V	1		32	MHz
Number of code flash rewrites	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

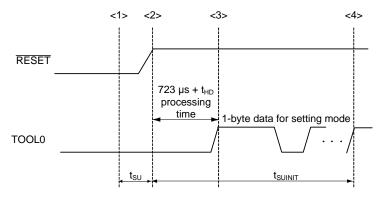
$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tнo	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

<R> 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS T_A = -40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to +105°C R5F140xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EV_{DD0}, EV_{DD1}, EV_{SS0}, or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD}, or replace EV_{SS0} and EV_{SS1} with V_{SS}.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product in the RL78/G13A User's Manual.
 - 4. Please contact Renesas Electronics sales office for derating of operation under T_A = +85°C to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13A is used in the range of $T_A = -40$ to +85°C, see 2. **ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)**.

There are following differences between the products "G: Industrial applications ($T_A = -40$ to +105°C)" and the products "A: Consumer applications".

Parameter	Api	olication
	A: Consumer applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C
Operating mode	HS (high-speed main) mode:	HS (high-speed main) mode only:
Operating voltage range	2.7 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 32 MHz	2.7 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 32 MHz
	2.4 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 16 MHz	2.4 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 16 MHz
	LS (low-speed main) mode:	
	1.8 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 8 MHz	
	LV (low-voltage main) mode:	
	1.6 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 4 MHz	
Serial array unit	UART	UART
	CSI: fclk/2 (supporting 16 Mbps), fclk/4	CSI: fclk/4
	Simplified I ² C communication	Simplified I ² C communication
IICA	Normal mode	Normal mode
	Fast mode	Fast mode
	Fast mode plus	
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V	Rise detection voltage: 2.61 V to 4.06 V
	(14 levels)	(8 levels)
	Fall detection voltage: 1.63 V to 3.98 V	Fall detection voltage: 2.55 V to 3.98 V
	(14 levels)	(8 levels)

(Remark is listed on the next page.)

Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products "A: Consumer applications". For details, refer to **3.1** to **3.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25^{\circ}C$) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	Virego	REGC	-0.3 to +2.1 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	Vıı	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2}	>
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo ₁	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 Note 2	V
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} +0.3 Note 2	V
Analog input voltage	Vai1	ANI16 to ANI20	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V
	V _{Al2}	ANI0 to ANI14	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V

- Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF}(+)$: Positive reference voltage of the A/D converter.
 - 3. Vss: Reference voltage



Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	- 40	mA
		Total of all pins -170 mA	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	–70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	-100	mA
	І ОН2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	100	mA
	lo _{L2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	Та	In normal operation	on mode	-40 to +105	°C
temperature		In flash memory	programming mode		
Storage temperature	T _{stg}			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	2.7 V ≤ V _{DD} ≤ 5.5 V	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	2.4 V ≤ V _{DD} < 2.7 V	1.0		16.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator** in the RL78/G13A User's Manual.

3.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін		1		32	MHz
High-speed on-chip oscillator clock frequency accuracy			-1.0		+1.0	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

3.3 DC Characteristics

3.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	2.4 V ≤ EVDD0 ≤ 5.5 V			-3.0 Note 2	mA
		Total of P00 to P04, P40 to P47, P102,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			-30.0	mA
		P120, P130, P140 to P145 (When duty ≤ 70% Note 3)	2.7 V ≤ EV _{DD0} < 4.0 V			-10.0	mA
		(When duty = 70% ***)	2.4 V ≤ EV _{DD0} < 2.7 V			-5.0	mA
		P50 to P57 P64 to P67 P70 to P77	4.0 V ≤ EV _{DD0} ≤ 5.5 V			-30.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V			-19.0	mA
		P146, P147 (When duty ≤ 70% Note 3)	2.4 V ≤ EV _{DD0} < 2.7 V			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ EV _{DD0} ≤ 5.5 V			-60.0	mA
	І ОН2	Per pin for P20 to P27, P150 to P156	2.4 V ≤ V _{DD} ≤ 5.5 V			-0.1 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ V _{DD} ≤ 5.5 V			-1.5	mA

- Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDDO, EVDD1, VDD pins to an output pin.
 - 2. Do not exceed the total current value.
 - 3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and loh = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	I _{OL1}	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147				8.5 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			40.0	mA
		P102, P120, P130, P140 to P145	2.7 V ≤ EV _{DD0} < 4.0 V			15.0	mA
		(When duty ≤ 70% Note 3)	2.4 V ≤ EV _{DD0} < 2.7 V			9.0	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			40.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V			35.0	mA
		P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% Note 3)	2.4 V ≤ EV _{DD0} < 2.7 V			20.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				80.0	mA
	lo _{L2}	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ V _{DD} ≤ 5.5 V			5.0	mA

- Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
 - 2. Do not exceed the total current value.
 - 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

Total output current of pins = (lo_L x 0.7)/(n x 0.01)

<Example> Where n = 80% and lol = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (3/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input voltage, high	V _{IH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8EVDDO		EV _{DD0}	V
			TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2		EV _{DD0}	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	2.0		EV _{DD0}	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	1.5		EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156	0.7V _{DD}		V _{DD}	V	
	V _{IH4}	P60 to P63	0.7EV _{DD0}		6.0	V	
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLKS	0.8V _{DD}		V _{DD}	V	
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ EV _{DD0} < 3.3 V	0		0.32	V
	V _{IL3}	P20 to P27, P150 to P156		0		0.3V _{DD}	V
	VIL4	P60 to P63		0		0.3EV _{DD0}	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS	RESET	0		0.2V _{DD}	٧

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (4/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	EV _{DD0} - 0.7			V
		P70 to P77, P80 to P87, P100 to P102, P110, P111, P120,	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -2.0 mA	EV _{DD0} - 0.6			V
		P130, P140 to P147	$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{I}_{\text{OH1}} = -1.5 \text{ mA}$	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \mu\text{A}$	V _{DD} - 0.5			V
Output voltage, low	V _{OL1}	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 8.5 mA			0.7	V
		P100 to P102, P110, P111, P120, P130, P140 to P147	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 3.0 mA			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 1.5 mA			0.4	V
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 0.6 mA			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL2} = 400 \mu\text{A}$			0.4	V
	Vоьз	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL3 = 15.0 mA			2.0	V
			$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL3 = 5.0 mA			0.4	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL3 = 3.0 mA			0.4	V
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iol3 = 2.0 mA			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (5/5)

Items	Symbol	Condit	ions		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішн1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVDD0				1	μА
	ILIH2	P20 to P27, P1 <u>37,</u> P150 to P156, RESET	Vı = Vdd	VI = VDD			1	μΑ
	Ішнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = V _{DD}	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
Input leakage current, low	IUL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	V _I = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss	Vı = Vss			-1	μΑ
	І LIL3	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pll-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVsso,	V _I = EVsso, In input port		20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/2)$

Parameter	Symbol	Conditions						TYP.	MAX.	Unit	
Supply	I _{DD1}	Operating	HS (high-	f _{IH} = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		1.5		mA	
current Note 1		mode	speed main) mode Note 5		operation	V _{DD} = 3.0 V		1.5		mA	
			mode		Normal	V _{DD} = 5.0 V		3.4	6.8	mA	
					operation	V _{DD} = 3.0 V		3.4	6.8	mA	
				f _{IH} = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		2.7	5.3	mA	
					operation	V _{DD} = 3.0 V		2.7	5.3	mA	
				fin = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		2	3.8	mA	
					operation	V _{DD} = 3.0 V		2	3.8	mA	
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.2	4.4	mA	
			speed main) mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		2.3	4.5	mA	
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.2	4.4	mA	
			VDD = 3.0 V	V _{DD} = 3.0 V	operation	Resonator connection		2.3	4.5	mA	
		Subsystem clock operation		Normal	Square wave input		1.2	2.4	mA		
			V _{DD} = 5.0 V	operation	Resonator connection		1.4	2.6	mA		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.2	2.4	mA	
			-	V _{DD} = 3.0 V	operation	Resonator connection		1.4	2.6	mA	
				fsub = 32.768 kHz	Normal operation	Square wave input		4	5.5	μΑ	
				operation		T _A = -40°C		Resonator connection		4	5.7
				fsub = 32.768 kHz	Normal operation	Square wave input		4.2	6.7	μΑ	
				T _A = +25°C		Resonator connection		4.3	6.9	μΑ	
				fsub = 32.768 kHz	Normal operation	Square wave input		4.5	9.3	μΑ	
				T _A = +50°C		Resonator connection		4.7	9.5	μΑ	
				fsub = 32.768 kHz	Normal operation	Square wave input		5.3	15.8	μΑ	
				T _A = +70°C	·	Resonator connection		5.6	16	μΑ	
				fsub = 32.768 kHz Note 4	Normal operation	Square wave input		6.6	25.8	μΑ	
			T _A = +85°C		Resonator connection		7.1	26	μΑ		
		fsu	fsub = 32.768 kHz	Normal operation	Square wave input		10.6	54.8	μΑ		
			T _A = +105°C		Resonator connection		11.4	55	μΑ		

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, EVDD1 or Vss, EVss0, EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz 2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$ (2/2)

Parameter	Symbol		Conditions					MAX.	Unit
Supply			HS (high-	fih = 32 MHz Note 4	V _{DD} = 5.0 V		0.41	1.71	mA
Current Note 1	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.41	1.71	mA
Note 1				f _{IH} = 24 MHz Note 4	V _{DD} = 5.0 V		0.34	1.35	mA
					V _{DD} = 3.0 V		0.34	1.35	mA
				f _{IH} = 16 MHz Note 4	V _{DD} = 5.0 V		0.33	1.04	mA
					V _{DD} = 3.0 V		0.33	1.04	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	1.05	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.37	1.26	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	1.05	mA
				V _{DD} = 3.0 V	Resonator connection		0.37	1.26	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.12	0.62	mA
				V _{DD} = 5.0 V	Resonator connection		0.22	0.73	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.12	0.62	mA
				V _{DD} = 3.0 V	Resonator connection		0.22	0.73	mA
		Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.39	1	μΑ	
			clock	T _A = -40°C	Resonator connection		0.48	1.3	μΑ
			operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.55	2.2	μΑ
				T _A = +25°C	Resonator connection		0.64	2.5	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.98	4.8	μΑ
				T _A = +50°C	Resonator connection		1.07	5.1	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.73	11.3	μΑ
				T _A = +70°C	Resonator connection		1.82	11.6	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		2.73	21.3	μΑ
				T _A = +85°C	Resonator connection		2.82	21.6	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		5.33	50.3	μΑ
				T _A = +105°C	Resonator connection		5.42	50.6	μΑ
	I _{DD3} Note 6	STOP	T _A = -40°C				0.26	0.7	μΑ
	mode ^{Note 8}	T _A = +25°C				0.42	1.9	μΑ	
			T _A = +50°C				0.85	4.5	μΑ
			T _A = +70°C				1.6	11	μΑ
			T _A = +85°C				2.6	21	μΑ
			T _A = +105°C				5.2	50	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDO, and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, EVDDO or Vss, EVsso, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - **4.** When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz to } 16 \text{ MHz}$

- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

Peripheral Functions (Common to all products)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	FIL Note 1				0.2		μΑ
RTC operating current	IRTC Notes 1, 2, 3				0.02		μΑ
12-bit interval timer operating current	I _{IT} Notes 1, 2, 4				0.02		μΑ
Watchdog timer operating current	WDT Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μΑ
A/D converter	IADC	When conversion	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
operating current	Notes 1, 6	at maximum speed	Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	ladref Note 1				100		μΑ
Temperature sensor operating current	ITMPS Note 1				100		μΑ
LVD operating current	I _{LVD}				0.02		μΑ
Self programming operating current	IFSP Notes 1, 9				2.5	12.2	mA
BGO operating current	BGO Notes 1, 8				2.5	12.2	mA
SNOOZE	Isnoz	ADC operation	The mode is performed Note 10		0.5	0.6	mA
operating current	Note 1		The A/D conversion operations are performed, low-voltage mode, AVREFP = VDD = 3.0 V		0.9	1.1	mA
		CSI/UART operation	1		0.5	0.62	mA

Notes 1. Current flowing to the VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
- 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter is in operation.



- Notes 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
 - 8. Current flowing only during data flash rewrite.
 - 9. Current flowing only during self programming.
 - 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13A User's Manual.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$

3.4 AC Characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Тсч	Main system clock (fmain) operation	HS (high-speed main) mode	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ $2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.03125 0.0625		1	µs µs
		Subsystem of operation	clock (fsuв)	2.4 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self	HS (high-speed	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
		programming mode	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
External system clock frequency	fex	2.7 V ≤ V _{DD} ≤	≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} <	< 2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock input high-	texh, texl	2.7 V ≤ V _{DD} ≤	≤ 5.5 V		24			ns
level width, low-level width		2.4 V ≤ V _{DD} < 2.7 V			30			ns
	texhs,				13.7			μs
TI00 to TI07, TI10 to TI13 input high-level width, low-level width	tтін, tтіL				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO13	f то	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	fpcL	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
Interrupt input high-level width,	tinth,	INTP0	2.4 V	≤ V _{DD} ≤ 5.5 V	1			μs
low-level width	tintl	INTP1 to INTP11 2.4 V ≤ EV _{DD0} ≤ 5.5 V		1			μs	
Key interrupt input low-level width	t kr	KR0 to KR7 2.4 V ≤ EV _{DD0} ≤ 5.5 V		250			ns	
RESET low-level width	trsL				10			μs

 $\textbf{Note} \quad \text{The following conditions are required for low voltage interface when } \textbf{E}_{VDD0} < \textbf{V}_{DD}$

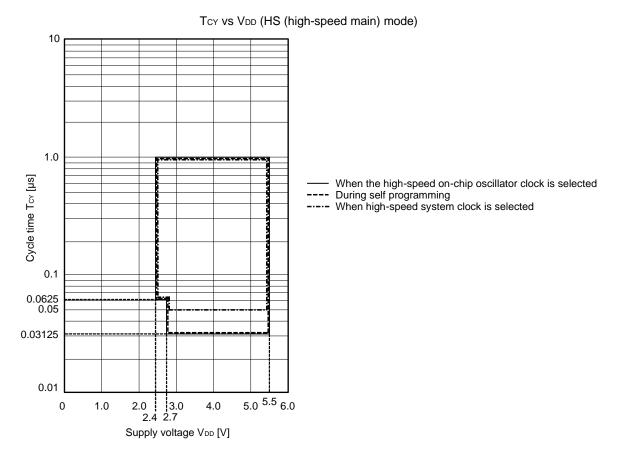
 $2.4V \le EV_{DD0} < 2.7 \text{ V}$: MIN. 125 ns

Remark fmck: Timer array unit operation clock frequency

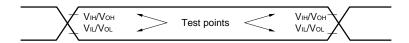
(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

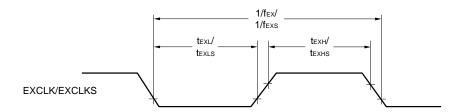
Minimum Instruction Execution Time during Main System Clock Operation



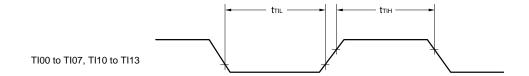
AC Timing Test Points

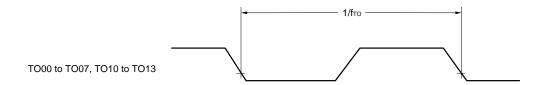


External System Clock Timing

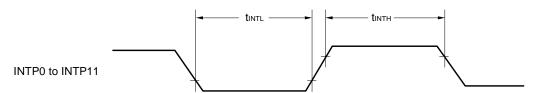


TI/TO Timing

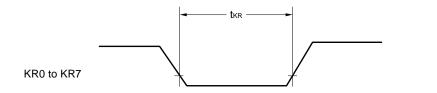




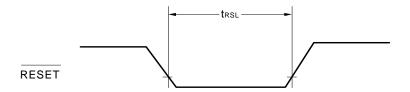
Interrupt Request Input Timing



Key Interrupt Input Timing

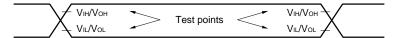


RESET Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

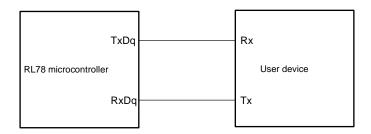
 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-spee	Unit	
				MIN.	MAX.	
Transfer rate Note 1					fmck/12 Note 2	bps
			Theoretical value of the maximum transfer rate fclk = 32 MHz, fMCK = fclk		2.6	Mbps

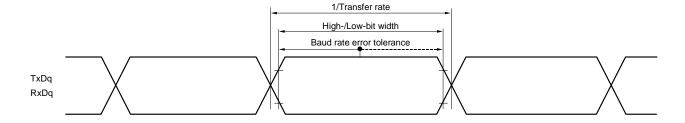
- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$. $2.4 \text{ V} \leq E_{VDD0} < 2.7 \text{ V}$: MAX. 1.3 Mbps

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.]
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	2.7 V ≤ EV _{DD0} ≤ 5.5 V	250		ns
			2.4 V ≤ EV _{DD0} ≤ 5.5 V	500		ns
SCKp high-/low-level width	tĸнı,	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tксү1/2 - 24		ns
	t _{KL1}	2.7 V ≤ EV _{DD0} ≤ 5.5 V		tксү1/2 - 36		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		tксү1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsıkı	4.0 V ≤ EV _{DD0} ≤ 5.5 V		66		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V		66		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		113		ns
SIp hold time (from SCKp↑) Note 2	tksi1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note	e 4		50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed ma	Unit	
				MIN.	MAX.	
SCKp cycle time Note 5	tkcy2	4.0 V ≤ EV _{DD0} ≤ 5.5 V	20 MHz < fмск	16/fмск		ns
			fмcк ≤ 20 MHz	12/fмск		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	16 MHz < fмск	16/fмск		ns
			fmck ≤ 16 MHz	12/fмск		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		16/fмск		ns
				12/fмск and 1000		ns
SCKp high-/low-level	tкн2, tкL2	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tксу2/2 - 14		ns
width		2.7 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 16		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 - 36		ns
SIp setup time	tsık2	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск+40		ns
(to SCKp↑) Note 1		2.4 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск+60		ns
SIp hold time (from SCKp↑) Note 2	tksi2	2.4 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск+62		ns
Delay time from SCKp↓ to SOp output Note 3	t KSO2	C = 30 pF Note 4	2.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+66	ns
			2.4 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+113	ns

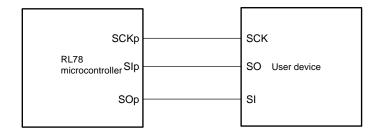
- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp\" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp†" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

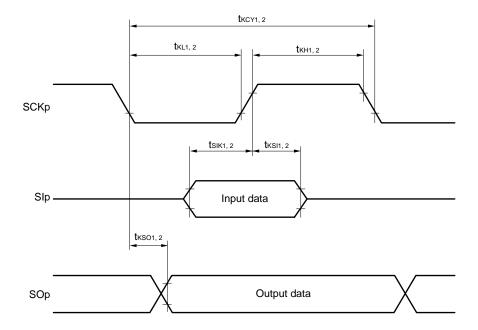
Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)

> 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

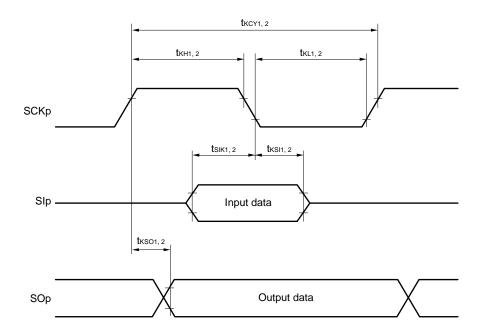
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(4) During communication at same potential (simplified I²C mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol Conditions		HS (high-speed main) Mode		Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		400 Note1	kHz
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$		100 Note1	kHz
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1200		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 3 \text{ k}Ω$	4600		ns
Hold time when SCLr = "H"	tніgн	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1200		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	4600		ns
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1/fmck + 220 Note2		ns
		2.4 V ≤ EV _{DD} ≤ 5.5 V, $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	1/f _{MCK} + 580 Note2		ns
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	770	ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	0	1420	ns

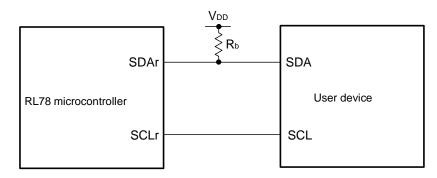
Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

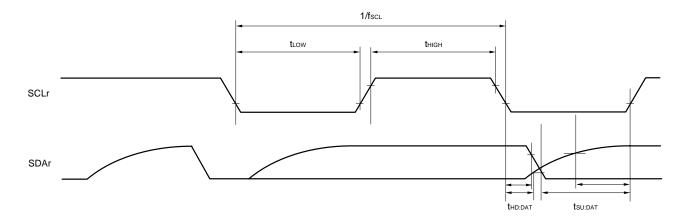
Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 44- and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

- 2. r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14), h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditio	ns	HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate		Reception	4.0 V ≤ EV _{DD0} ≤ 5.5 V,			fmck/12 Note 1	bps
			2.7 V ≤ V _b ≤ 4.0 V	Theoretical value of the maximum transfer rate fclk = 32 MHz, fMck = fclk		2.6	Mbps
			2.7 V ≤ EV _{DD0} < 4.0 V,			fмск/12 Note 1	bps
			$2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}$ $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}$	Theoretical value of the maximum transfer rate fclk = 32 MHz, fMck = fclk		2.6	Mbps
						fMCK/12 Notes 1,2	bps
		Theoretical value of the maximum transfer rate fclk = 32 MHz, fMck = fclk		2.6	Mbps		

- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The following conditions are required for low voltage interface when E_{VDD0} < V_{DD} .

 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 44 and 48-pin products)/EV_{DD} tolerance (for the 64- and 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)
- **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions			HS (high-spe	ed main) Mode	Unit
					MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV _{DD0} ≤ 5.5 V,			Note 1	bps
			$2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.6 Note 2	Mbps
			2.7 V ≤ EV _{DD0} < 4.0 V,	,		Note 3	bps
			$2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}$	Theoretical value of the maximum transfer rate		1.2 Note 4	Mbps
				$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$			
		2.4 V ≤ EV _{DD0} < 3.3 V,			Note 5	bps	
		1.6 V ≤ V _b ≤ 2.0 V	Theoretical value of the maximum transfer rate		0.43 Note 6	Mbps	
				$C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$			

Notes 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV_{DD0} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

$$\label{eq:maximum transfer rate} \begin{aligned} & \frac{1}{\{-C_b \times R_b \times ln\ (1\ -\frac{2.2}{V_b})\} \times 3} \ [bps] \end{aligned}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD0} < 4.0 V and 2.4 V ≤ V_b ≤ 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

Notes 5. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

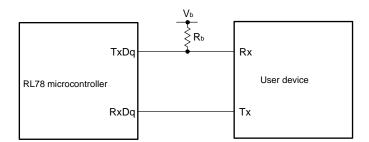
$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1 - \frac{1.5}{V_b})\} \times 3} \text{[bps]}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{1.5}{V_b})}\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

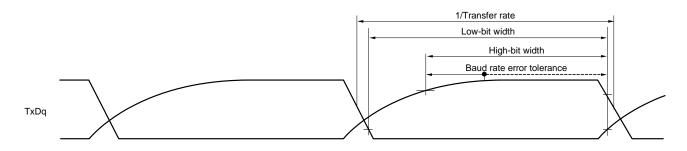
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

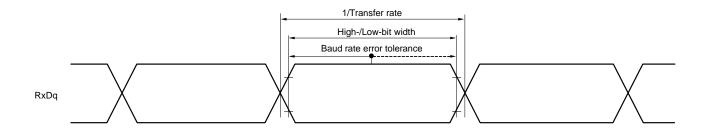
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 44-and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- Remarks 1. $R_b[\Omega]$:Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	tkcY1	tkcy1 ≥ 4/fclk	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	600		ns
			$C_b = 30$ pF, $R_b = 1.4$ k Ω			
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	1000		ns
			$C_b = 30 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	2300		ns
			$C_b = 30$ pF, $R_b = 5.5$ k Ω			
SCKp high-level width	el width tкн1 4.0 V ≤		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$			ns
		$C_b = 30 \text{ pF, } R_b = 1.4 \text{ k}\Omega$				
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		tксү1/2 - 340		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ $2.4 \text{ V} \le \text{EV}_{DD0} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V},$				
				tkcy1/2 - 916		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$				
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD}	$0 \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	tксү1/2 - 24		ns
		C _b = 30 pF, R	$R_b = 1.4 \text{ k}\Omega$			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		tксү1/2 - 36		ns
		C _b = 30 pF, R	$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ $2.4 \text{ V} \le \text{EV}_{DD0} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V},$			
		2.4 V ≤ EV _{DD0}				ns
		C _b = 30 pF, R	$R_b = 5.5 \text{ k}\Omega$			

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 44- and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spe	ed main) Mode	Unit
			MIN.	MAX.	
SIp setup time	tsıĸ1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	162		ns
(to SCKp↑) Note		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	354		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	958		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$			
SIp hold time (from SCKp↑) Note	tksıı	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	38		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	38		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	38		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
Delay time from SCKp↓ to	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$		200	ns
SOp output Note		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		390	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$		966	ns
		$C_b=30~pF,~R_b=5.5~k\Omega$			

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (Vpd tolerance (for the 44- and 48-pin products)/EVpd tolerance (for the 64- and 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

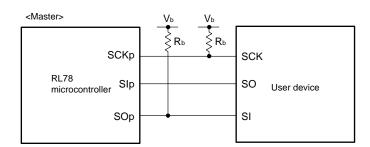
Parameter	Symbol	Conditions	HS (high-spe	ed main) Mode	Unit
			MIN.	MAX.	
SIp setup time	tsik1	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$	88		ns
(to SCKp↓) Note		$C_b = 30$ pF, $R_b = 1.4$ k Ω			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	88		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	220		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω			
SIp hold time	tksi1	$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$	38		ns
(from SCKp↓) Note		$C_b = 30$ pF, $R_b = 1.4$ k Ω			
		$2.7 \text{ V} \le \text{EV}_{DD0} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$	38		ns
		$C_b = 30$ pF, $R_b = 2.7$ k Ω			
		$2.4 \text{ V} \le \text{EV}_{DD0} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V},$	38		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω			
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$		50	ns
SOp output Note		$C_b = 30$ pF, $R_b = 1.4$ k Ω			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		50	ns
		$C_b = 30$ pF, $R_b = 2.7$ k Ω			
		$2.4 \text{ V} \le \text{EV}_{DD0} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V},$		50	ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω			

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (Vpd tolerance (for the 44- and 48-pin products)/EVpd tolerance (for the 64- and 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

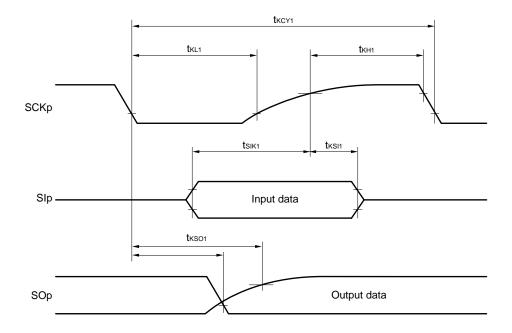
(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

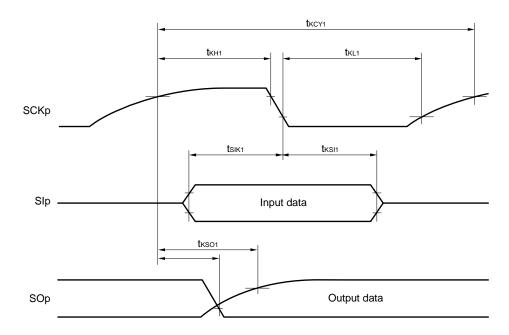


- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 of 48- and 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48- and 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

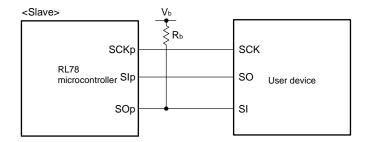
Parameter	Symbol	Conditions		HS (high-spe	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	4.0 V ≤ EV _{DD0} ≤ 5.5 V,	24 MHz < fмск	28/fмск		ns
		2.7 V ≤ V _b ≤ 4.0 V	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
			8 MHz < fмcк ≤ 20 MHz	20/fмск		ns
			4 MHz < fMCK ≤ 8 MHz	16/f мск		ns
			f _{MCK} ≤ 4 MHz	12/fмск		ns
		2.7 V ≤ EV _{DD0} < 4.0 V,	24 MHz < fмск	40/fмск		ns
		2.3 V ≤ V _b ≤ 2.7 V	20 MHz < fмcк ≤ 24 MHz	32/fмск		ns
			16 MHz < fмcк ≤ 20 MHz	28/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	24/fмск		ns
			4 MHz < fMCK ≤ 8 MHz	16/f мск		ns
			fmck ≤ 4 MHz	12/fмск		ns
		2.4 V ≤ EV _{DD0} < 3.3 V,	24 MHz < fмск	96/fмск		ns
		1.6 V ≤ V _b ≤ 2.0 V	20 MHz < fмcк ≤ 24 MHz	72/fмск		ns
			16 MHz < fмcк ≤ 20 MHz	64/f мск		ns
			8 MHz < fмcк ≤ 16 MHz	52/f мск		ns
			4 MHz < fMCK ≤ 8 MHz	32/fмск		ns
			fmck ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level width	tkH2,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	V,	tkcy2/2 - 24		ns
		$2.7 \text{ V} \le \text{EV}_{DD0} < 4.0$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$	V,	txcy2/2 - 36		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{N}_{\text{c}}}$		tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) Note2	tsık2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	V,	1/fмск + 40		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	V,	1/fмск + 40		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$	V,	1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 3	tksi2			1/fmck + 62		ns
Delay time from SCKp↓ to SOp output Note 4	tks02	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5$ $C_b = 30 \text{ pF}, R_b = 1.4$	V , 2.7 $V \le V_b \le 4.0 V$, $4 k\Omega$		2/fмск + 240	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7$	$V, 2.3 \ V \le V_b \le 2.7 \ V, 7 \ k\Omega$		2/fмск + 428	ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3$ C _b = 30 pF, R _b = 5.5	V, 1.6 V ≤ V _b ≤ 2.0 V 5 kΩ		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the next page.)

- Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance (for the 44- and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

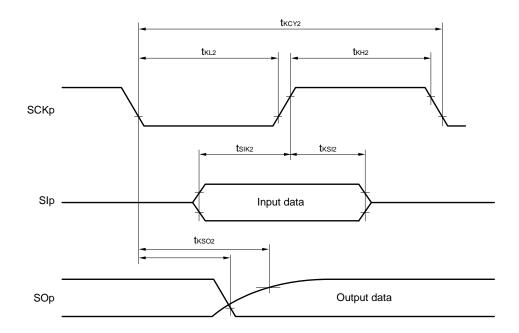
CSI mode connection diagram (during communication at different potential)



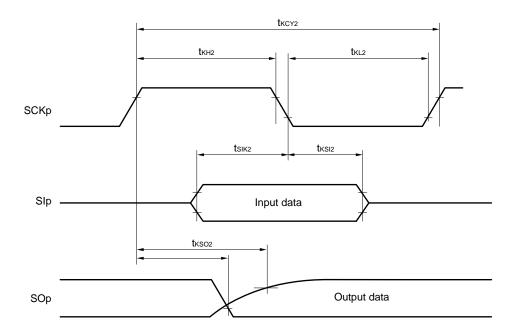
- **Remarks 1.** R_b[Ω]:Communication line (SOp) pull-up resistance, C_b[F]: Communication line (SOp) load capacitance, V_b[V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48- and 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

RENESAS

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48- and 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-s	speed main) ode	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$ \begin{aligned} &4.0 \; \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &C_{\text{b}} = 50 \; \text{pF}, \; R_{\text{b}} = 2.7 \; \text{k}\Omega \end{aligned} $		400 Note 1	kHz
		$ 2.7 \ V \le EV_{DD0} < 4.0 \ V, $ $ 2.3 \ V \le V_b \le 2.7 \ V, $ $ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega $		400 Note 1	kHz
				100 Note 1	kHz
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$		100 Note 1	kHz
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega$		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$ \begin{aligned} &4.0 \; \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &C_{\text{b}} = 50 \; \text{pF}, \; R_{\text{b}} = 2.7 \; \text{k}\Omega \end{aligned} $	1200		ns
			1200		ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	4600		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	4600		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	4650		ns
Hold time when SCLr = "H"	tнієн	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	620		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	500		ns
		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ k}\Omega$	2700		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	2400		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	1830		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-sp Mo		Unit
			MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	1/fmck + 340 Note 2		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega $	1/fмск + 340 Note 2		ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	1/f _{MCK} + 760 Note 2		ns
			1/fmck + 760 Note 2		ns
			1/fмск + 570 Note 2		ns
Data hold time (transmission)	thd:dat	$4.0 \text{ V} \le \text{EV}_{\text{DDO}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	770	ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega $	0	770	ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	0	1420	ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	0	1420	ns
			0	1215	ns

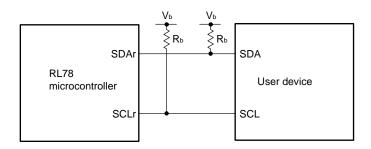
Notes 1. The value must also be equal to or less than fmck/4.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 44- and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 44- and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

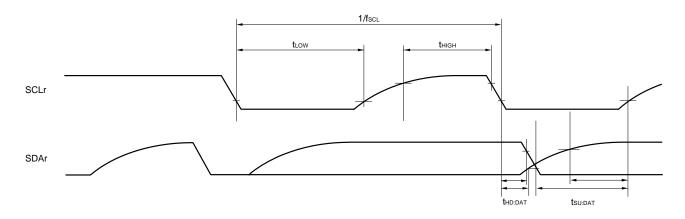
(Remarks are listed on the next page.)

^{2.} Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 44- and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 44- and 48-pin products)/EVDD tolerance (for the 64- and 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VH and VIL, see the DC characteristics with TTL input buffer selected.

- Remarks 1. R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13)

3.5.2 Serial interface IICA

Parameter	Symbol	Conditions	HS (h	HS (high-speed main) Mode			Unit
			Standa	rd Mode	Fast	Mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fclk ≥ 3.5 MHz	-	-	0	400	kHz
		Standard mode: fcLk ≥ 1 MHz	0	100	ı	_	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μs
Hold time ^{Note 1}	thd:sta		4.0		0.6		μs
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μs
Hold time when SCLA0 = "H"	t HIGH		4.0		0.6		μs
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu:sto		4.0		0.6		μs
Bus-free time	t BUF		4.7		1.3		μs

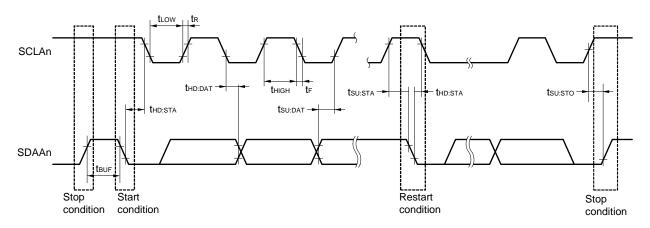
- **Notes 1.** The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



Remark n = 0, 1

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage							
Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = VDD Reference voltage (-) = Vss	Reference voltage (+) = VBGR Reference voltage (-) = AVREFM						
input channel	Reference voltage (-) = AVREFM	Reference voltage (-) = vss	Reference voltage (-) = AVREEM						
ANI0 to ANI14	Refer to 3.6.1 (1) .	Refer to 3.6.1 (3) .	Refer to 3.6.1 (4) .						
ANI16 to ANI20	Refer to 3.6.1 (2) .								
Internal reference voltage	Refer to 3.6.1 (1) .		_						
Temperature sensor output									
voltage									

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target pin: ANI2 to ANI14	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
		10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.375		39	μs
		Target pin: Internal reference	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR
Integral linearity error	ILE	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±1.5	LSB
Analog input voltage	Vain	ANI2 to ANI14	•	0		AVREFP	V
		Internal reference voltage outpo (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-			V _{BGR} Note 4		V
		Temperature sensor output vol· (2.4 V ≤ VDD ≤ 5.5 V, HS (high-	•		V _{TMPS25} Note	4	V

(Notes are listed on the next page.)

- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.
 Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

4. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI16 to ANI20

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq \text{EV}_{DD0} = \text{EV}_{DD1} \leq \text{V}_{DD} \leq 5.5 \text{ V}, 2.4 \text{ V} \leq \text{AV}_{REFP} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V},$ Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target pin : ANI16 to ANI20	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale errorNotes 1, 2	Ezs	10-bit resolution EVDD0 ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution EVDD0 ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution EVDD0 ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±3.5	LSB
Differential linearity error	DLE	10-bit resolution EVDD0 ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI20		0		AVREFP and EVDD0	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AVREFP = VDD.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

4. When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.

Overall error: Add ±4.0 LSB to the MAX. value when AVREFP = VDD.

Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AVREFP = VDD.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq \text{EV}_{DD0} = \text{EV}_{DD1} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{DD}, \text{Reference voltage (-)} = \text{V}_{SS})$

Parameter	Symbol	Condition	s	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target pin: ANI0 to ANI14,	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
		ANI16 to ANI20	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
		Target pin: Internal reference	2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
	sensor output	voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale errorNotes 1, 2	Ezs	10-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±0.60	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
Differential linearity error	DLE	10-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI14	•	0		V _{DD}	V
		ANI16 to ANI20		0		EV _{DD0}	V
		Internal reference voltage output (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)			V _{BGR} Note 3		V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)		,	V _{TMPS25} Note	3	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI20

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{BGR} Note ³, Reference voltage (-) = AV_{REFM} Note ⁴ = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Cond	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	VAIN			0		V _{BGR} Note 3	V

- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.
 - 4. When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.
 Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

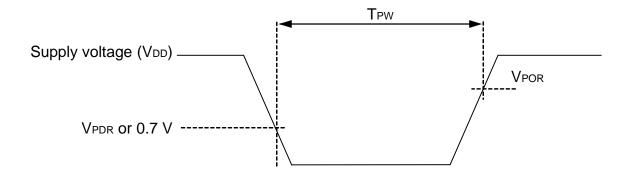
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, TA = +25°C		1.14		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature dependence of the temperature sensor		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

3.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	The power supply voltage is rising.		1.51	1.57	V
	V _{PDR}	The power supply voltage is falling.	1.44	1.50	1.56	V
Minimum pulse width Note	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage VLVD0		The power supply voltage is rising.		4.06	4.22	V
		The power supply voltage is falling.	3.83	3.98	4.13	V
	V _{LVD1}	The power supply voltage is rising.	3.60	3.75	3.90	V
		The power supply voltage is falling.	3.53	3.67	3.81	V
	V _{LVD2}	The power supply voltage is rising.	3.01	3.13	3.25	V
		The power supply voltage is falling.	2.94	3.06	3.18	V
	V _{LVD3}	The power supply voltage is rising.	2.90	3.02	3.14	V
		The power supply voltage is falling.	2.85	2.96	3.07	V
	V _{LVD4}	The power supply voltage is rising.	2.81	2.92	3.03	V
		The power supply voltage is falling.	2.75	2.86	2.97	V
	V _{LVD5}	The power supply voltage is rising.	2.70	2.81	2.92	V
		The power supply voltage is falling.	2.64	2.75	2.86	V
	V _{LVD6}	The power supply voltage is rising.	2.61	2.71	2.81	V
		The power supply voltage is falling.	2.55	2.65	2.75	V
	V _{LVD7}	The power supply voltage is rising.	2.51	2.61	2.71	V
		The power supply voltage is falling.	2.45	2.55	2.65	V
Minimum pulse width	tuw		300			μs
Detection delay time					300	μs

LVD Detection Voltage of Interrupt & Reset Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol	Con	MIN.	TYP.	MAX.	Unit	
Detection voltage	V _L VDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1,	POC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage		2.75	2.86	٧
	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	٧
			Falling interrupt voltage	2.75	2.86	2.97	٧
	V _{LVDD2}	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	٧
			Falling interrupt voltage	2.85	2.96	3.07	٧
	V _L VDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	٧
			Falling interrupt voltage	3.83	3.98	4.13	٧

3.6.5 Power supply voltage rising slope characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

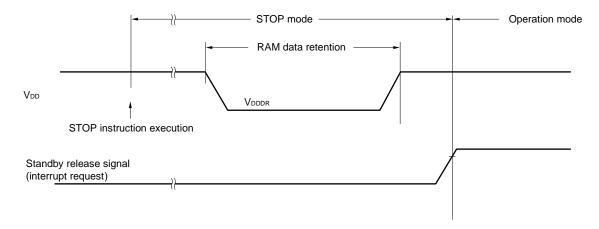
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	2.4 V ≤ VDD ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C Note 4	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C Note 4	100,000			
		Retained for 20 years TA = 85°C Note 4	10,000			

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer and Renesas Electronics self programming library.
 - **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 - **4.** This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

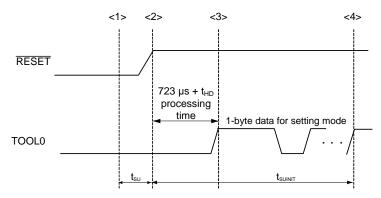
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tнo	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

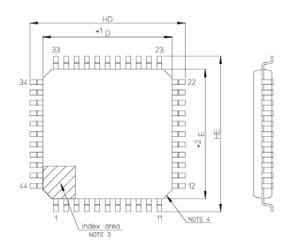
thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

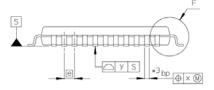
4. PACKAGE DRAWINGS

4.1 44-pin Products

R5F140FKAFP, R5F140FLAFP R5F140FKGFP, R5F140FLGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP44-10x10-0.80	PLQP0044GC-D	_	0.36g





- DIMENSIONS "A!" AND "A2" DO NOT INCLUDE MOLD FLASH, DIMENSION "A3" DOES NOT INCLUDE TRIM OFFSET. PN 1 VISUAL, INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

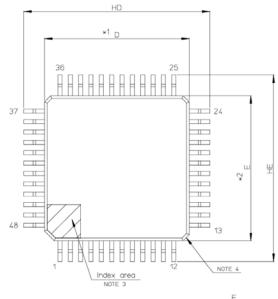
A1 A2 A2 A3	0025
Detail F	L1

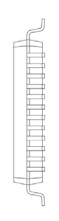
Reference	Dimens	ion in Mil	limeters
Symbol	Min	Nom	Max
D	9.8	10.0	10.2
Е	9.8	10.0	10.2
A2	_	1.4	
HD	11.8	12.0	12.2
HE	11.8	12.0	12.2
Α			1.6
A1	0.05		0.15
bp	0.22	0.37	0.45
С	0.09		0.20
θ	0*	3.5°	8*
е		0.80	
×	_		0.20
У		_	0.10
Lp	0.45	0.6	0.75
L1		1.0	

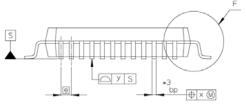
4.2 48-pin Products

R5F140GKAFB, R5F140GLAFB R5F140GKGFB, R5F140GLGFB

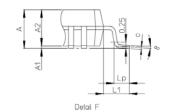
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LF0FP48-7x7-0.50	PLQP0048KB-B	_	0.2g









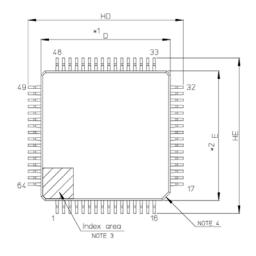


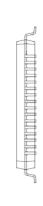
Reference	Dimension in Millimeters		
Symbol	Min	Nom	Max
D	6.9	7.0	7.1
Е	6.9	7.0	7.1
A2	_	1.4	_
HD	8.8	9.0	9.2
HE	8.8	9.0	9.2
Α			1.7
A1	0.05		0.15
bp	0.17	0.20	0.27
C	0.09		0.20
θ	0*	3.5°	8*
е	_	0.5	
×		_	0.08
У			0.08
Lp	0.45	0.6	0.75
L1		1.0	_

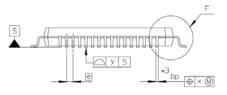
4.3 64-pin Products

R5F140LKAFB, R5F140LLAFB R5F140LKGFB, R5F140LLGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LF0FP64-10x10-0.50	PLQP0064KB-C	_	0.3g







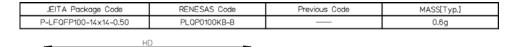
- DIMENSIONS "4" AND "42" DO NOT INCLUDE MOLD FLASH.
 DIMENSION "43" DOES NOT INCLUDE TRIM OFFSET,
 PIN 1 VISUAL, INDEX FEATURE MAY VARY, BUT MUST BE
 LOCATED WITHIN THE HATCHED AREA.
 CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

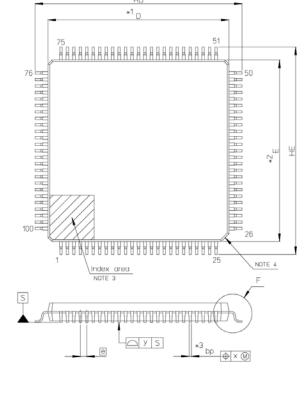
Detail F

Reference	Dimension in Millimeters		
Symbol	Min	Nom	Max
D	9.9	10.0	10.1
Е	9.9	10.0	10.1
A2		1.4	_
HD	11.8	12.0	12.2
HE	11.8	12.0	12.2
А			1.7
A1	0.05		0.15
bp	0.15	0.20	0.27
С	0.09		0.20
θ	0*	3.5°	8 *
е		0.5	_
×			0.08
У		_	0.08
Lp	0.45	0.6	0.75
L1		1.0	

4.4 100-pin Products

R5F140PKAFB, R5F140PLAFB R5F140PKGFB, R5F140PLGFB







A1 A2		0.25	
		Lp	_
		L1	
	Detail	F	

Reference	Dimension in Millimeters			
Symbol	Min	Nom	Max	
D	13.9	14.0	14.1	
Е	13.9	14.0	14.1	
A2	_	1.4	_	
HD	15.8	16.0	16.2	
HE	15.8	16.0	16.2	
А			1.7	
A1	0.05		0.15	
bp	0.15	0.20	0.27	
С	0.09		0.20	
θ	0*	3.5°	8 *	
е	_	0.5		
×	_		0.08	
У	_		0.08	
Lp	0.45	0.6	0.75	
L1		1.0		

Revision History	RL78/G13A Datasheet

		Description	
Rev.	Date	Page	Summary
1.00	Mar 06, 2020	-	First edition issued
1.10	Sep 18, 2020	18	Deletion of "(TARGET)" from the title of chapter 2 ELECTRICAL SPECIFICATIONS (T _A = -40 to +85°C)
		79	Deletion of "(TARGET)" from the title of chapter 3 ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

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The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

- 6. Voltage application waveform at input pin
 - Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).
- 7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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MB90F342ESPMC-G-JNE1 MB90022PF-GS-358E1 MB96F395RWAPMC-GSE2 MB96395RSAPMC-GS-110E2 MB90F883CSPMC-GE1

S912ZVHY64F1CLL S912ZVHY64F1VLQ ST10F280 MB96F338RSAPMCR-GK5E2 CY90096PF-G-002-BND-ERE1 ML62Q1569-NNNGAZ0AX ML62Q1739-NNNGAZ0AX ML62Q1749-NNNGAZ0AX ML62Q1579-NNNGAZ0AX ML62Q1559-NNNGAZ0AX ML62Q1729-NNNGAZ0AX